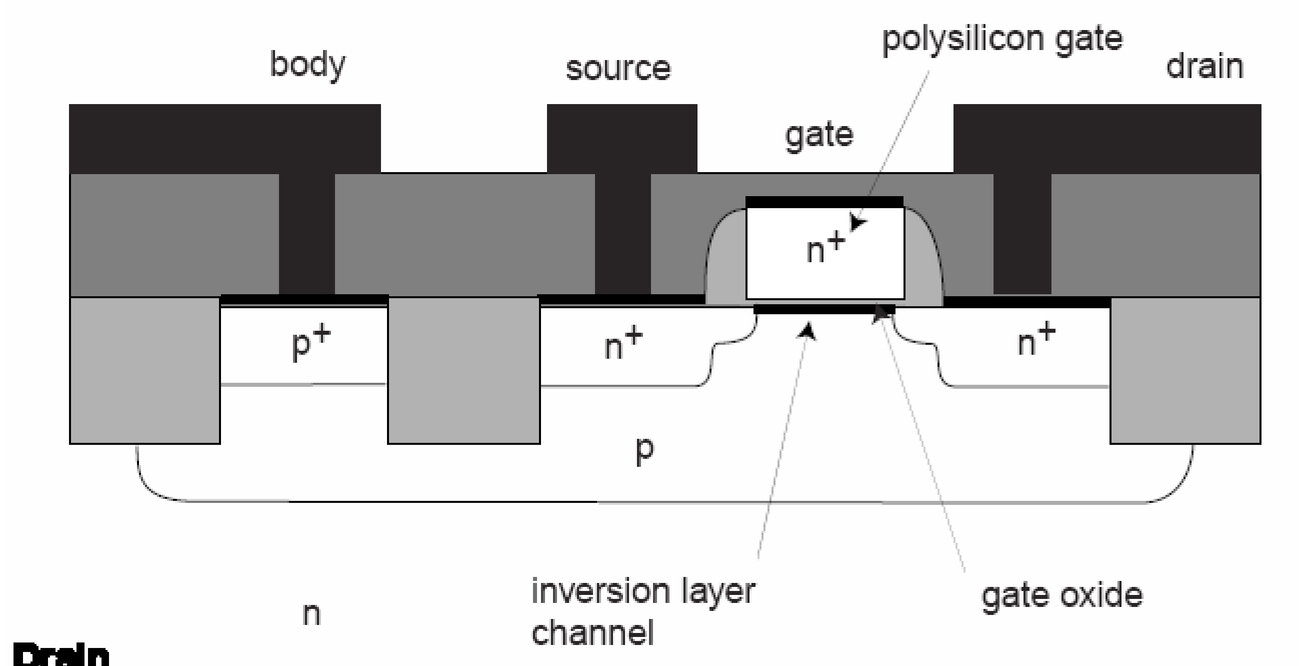
Technische Universität Graz

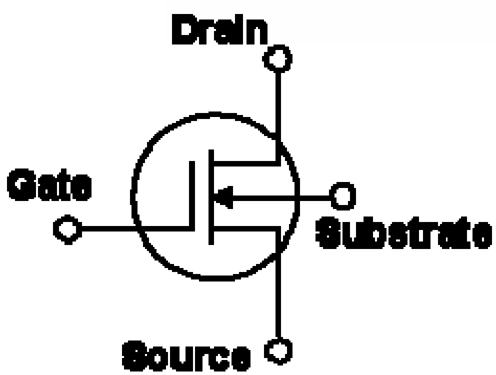
10. MOSFETs

Dec. 5, 2018

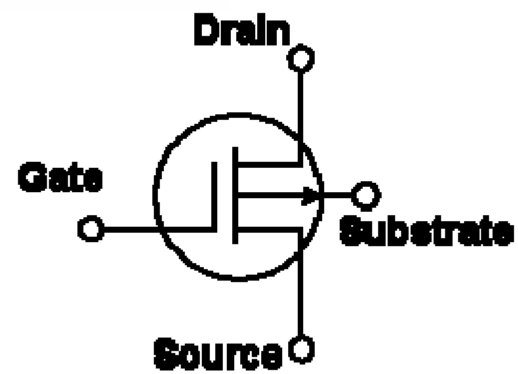
MOSFETs



functions as a switch
~ 1 billion /chip

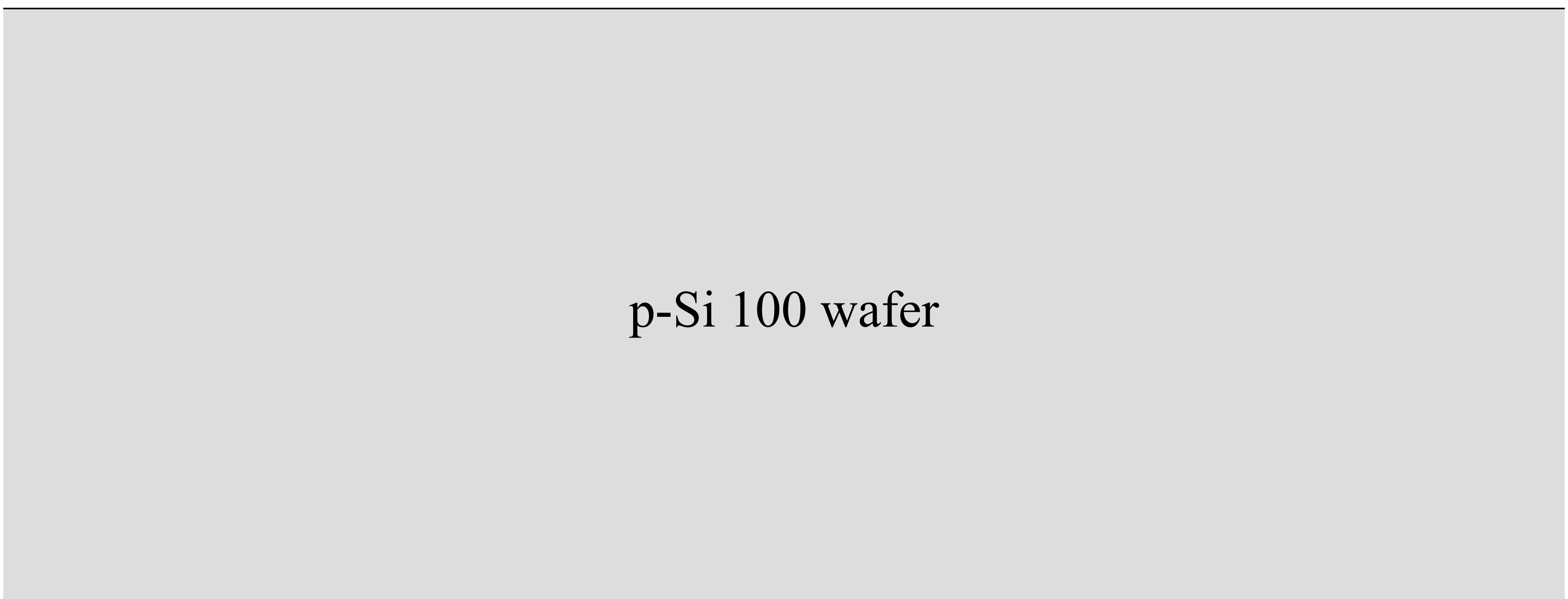


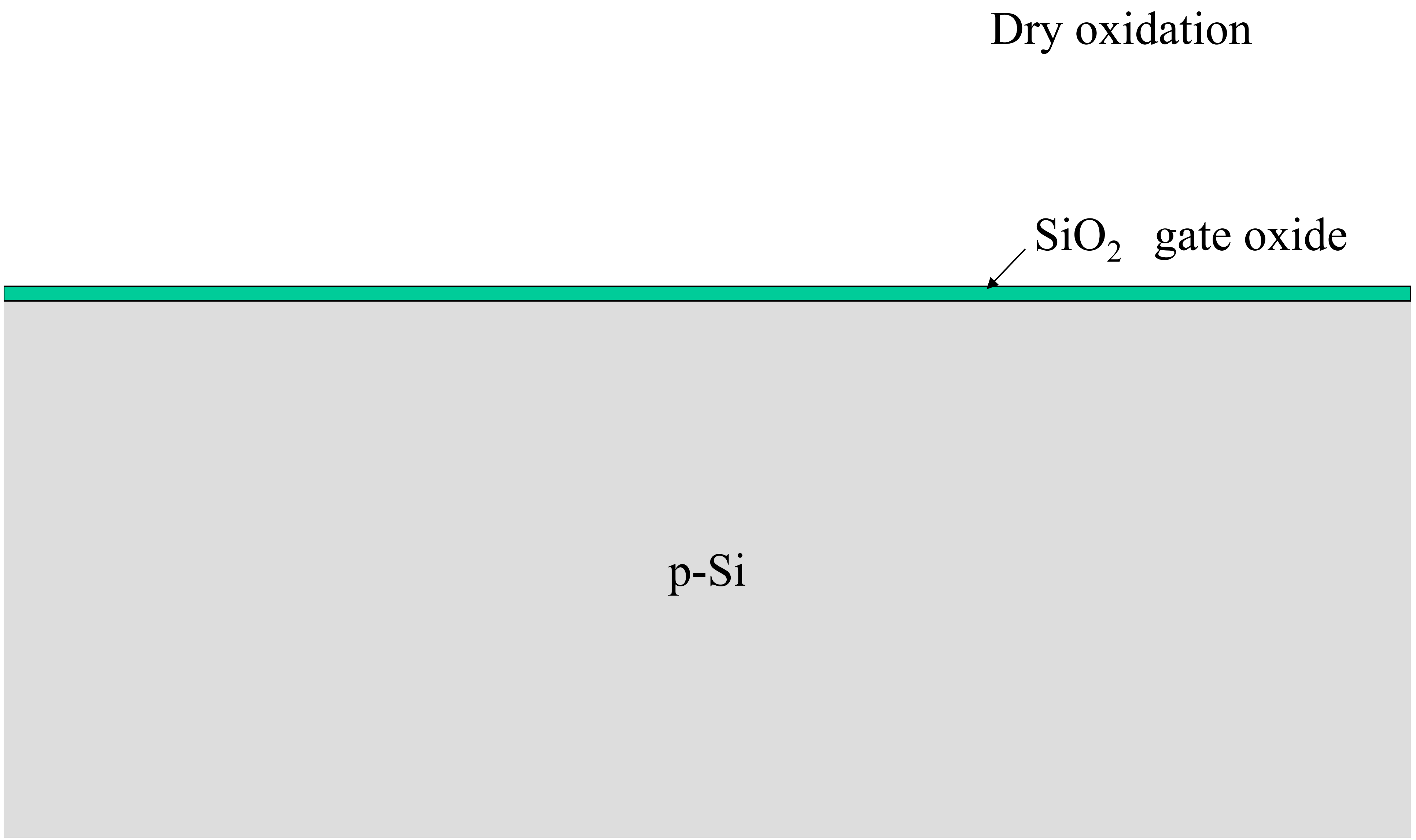
n - channel

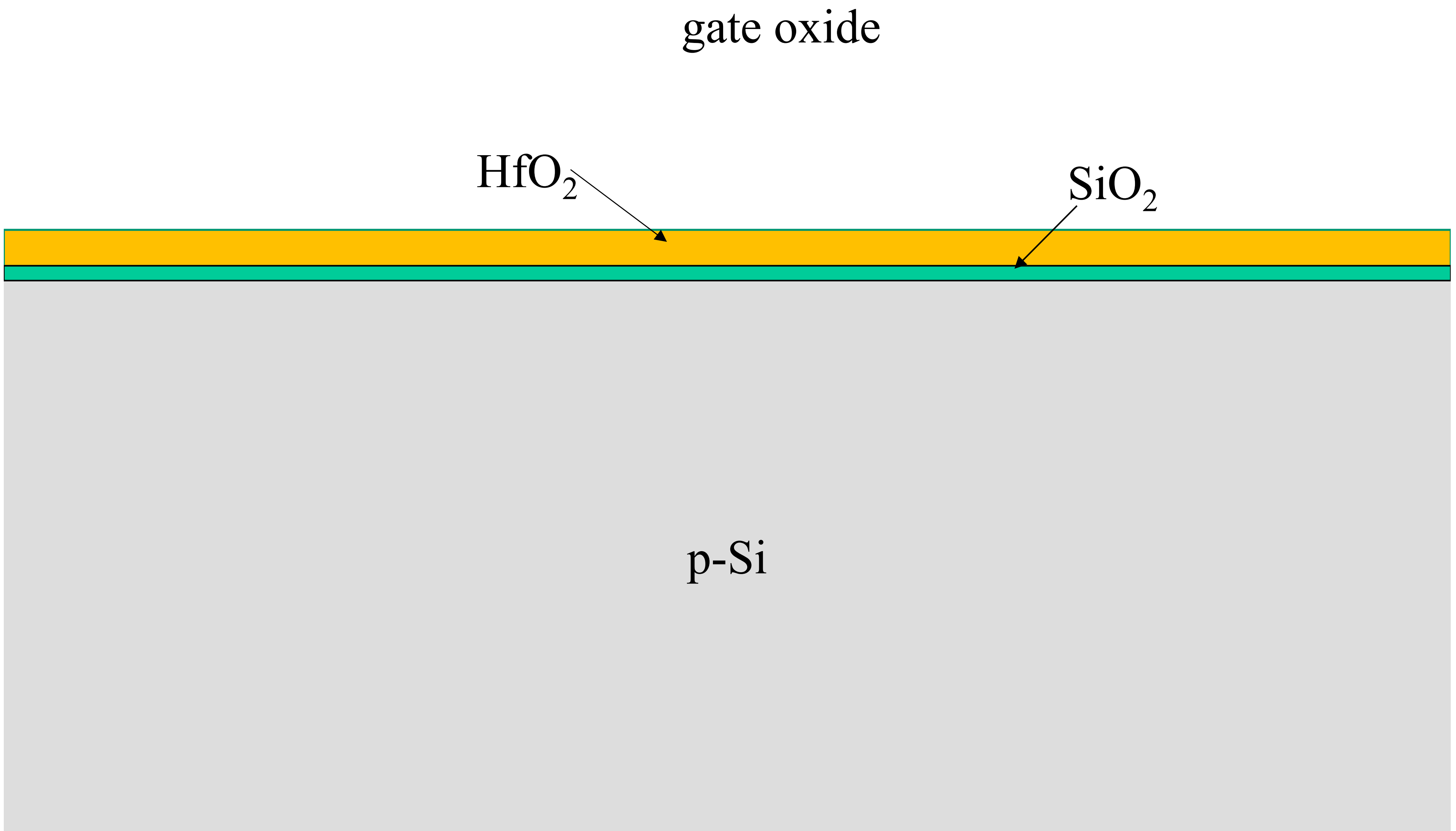


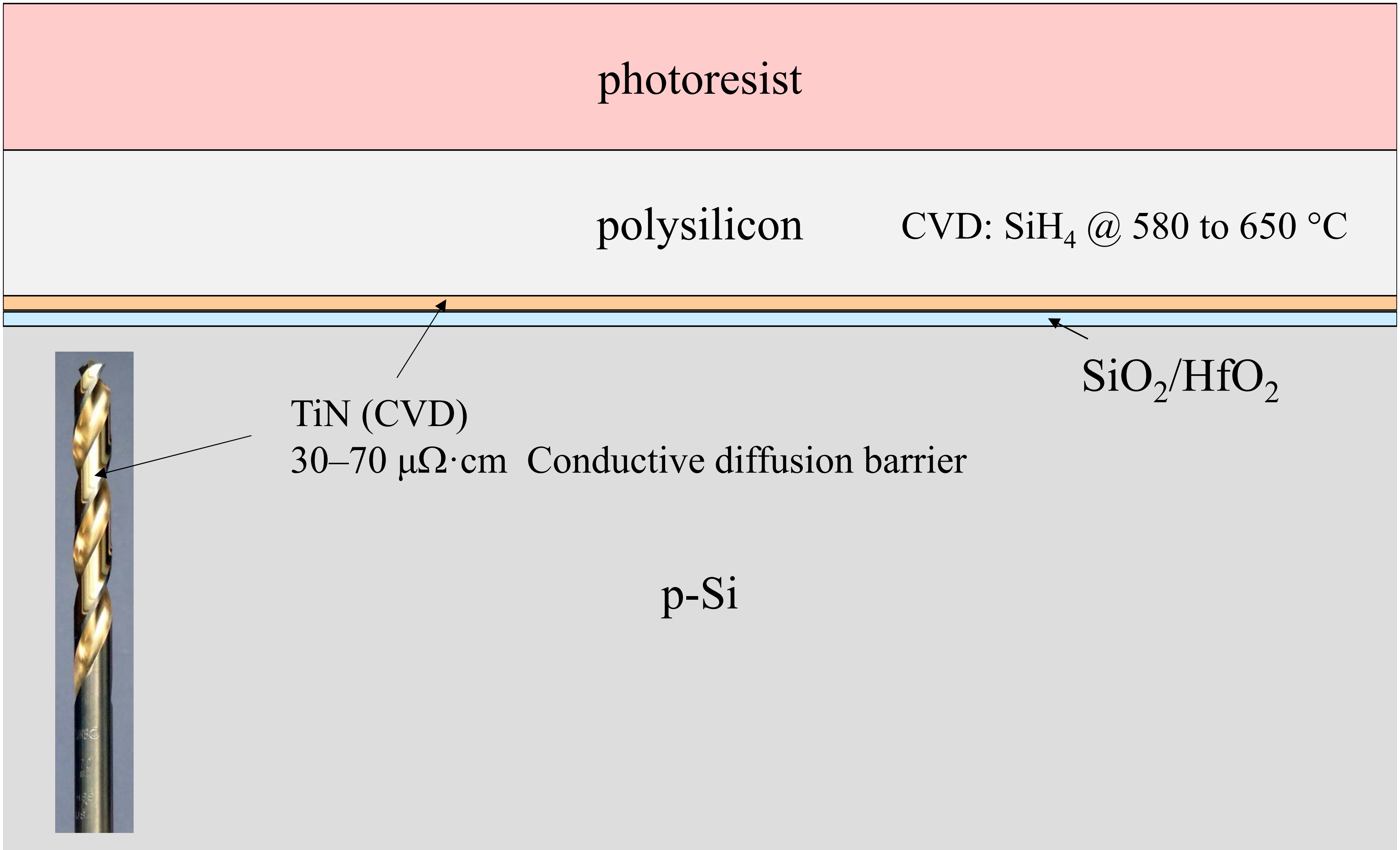
p - channel

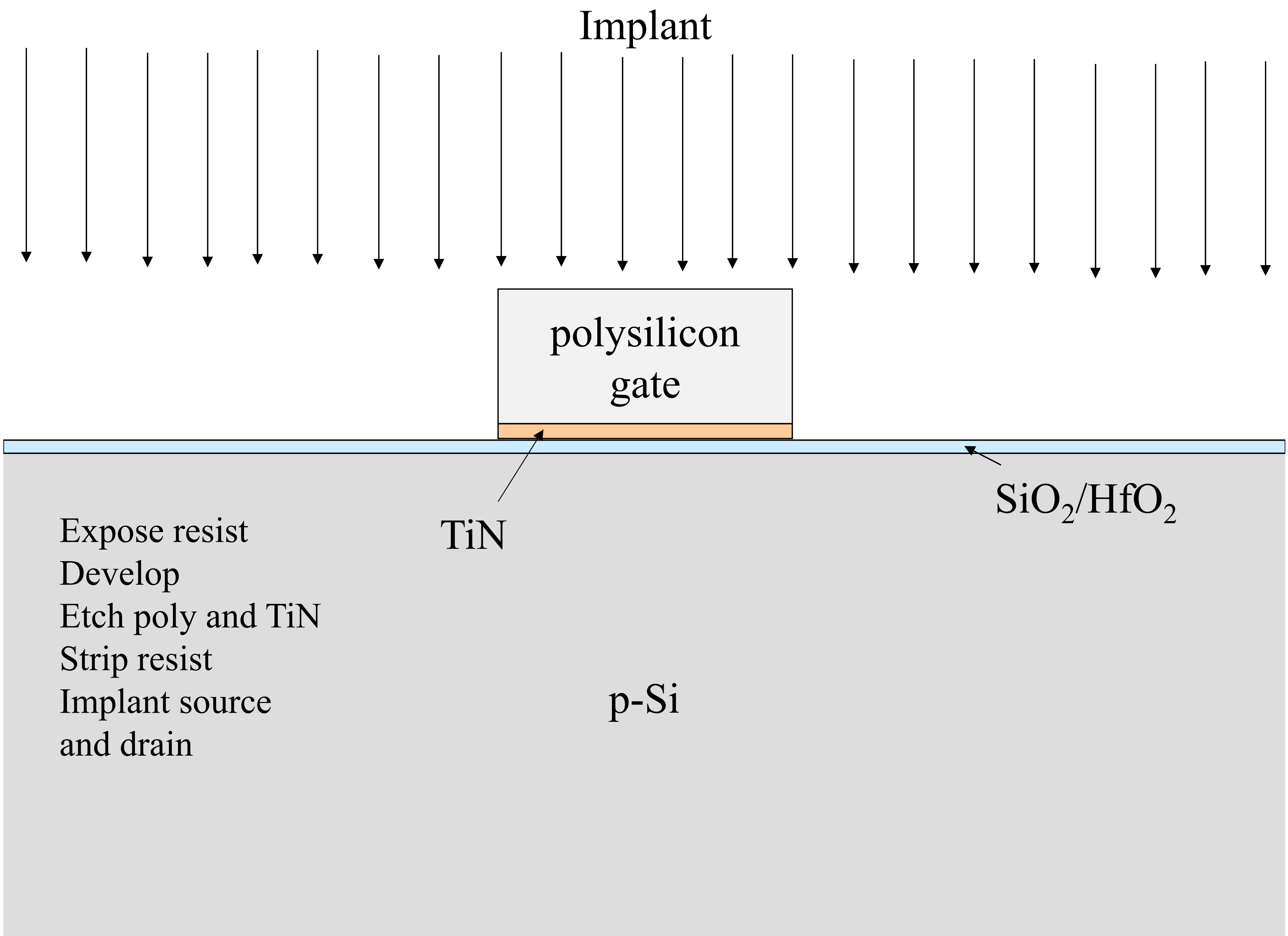
Self-aligned fabrication



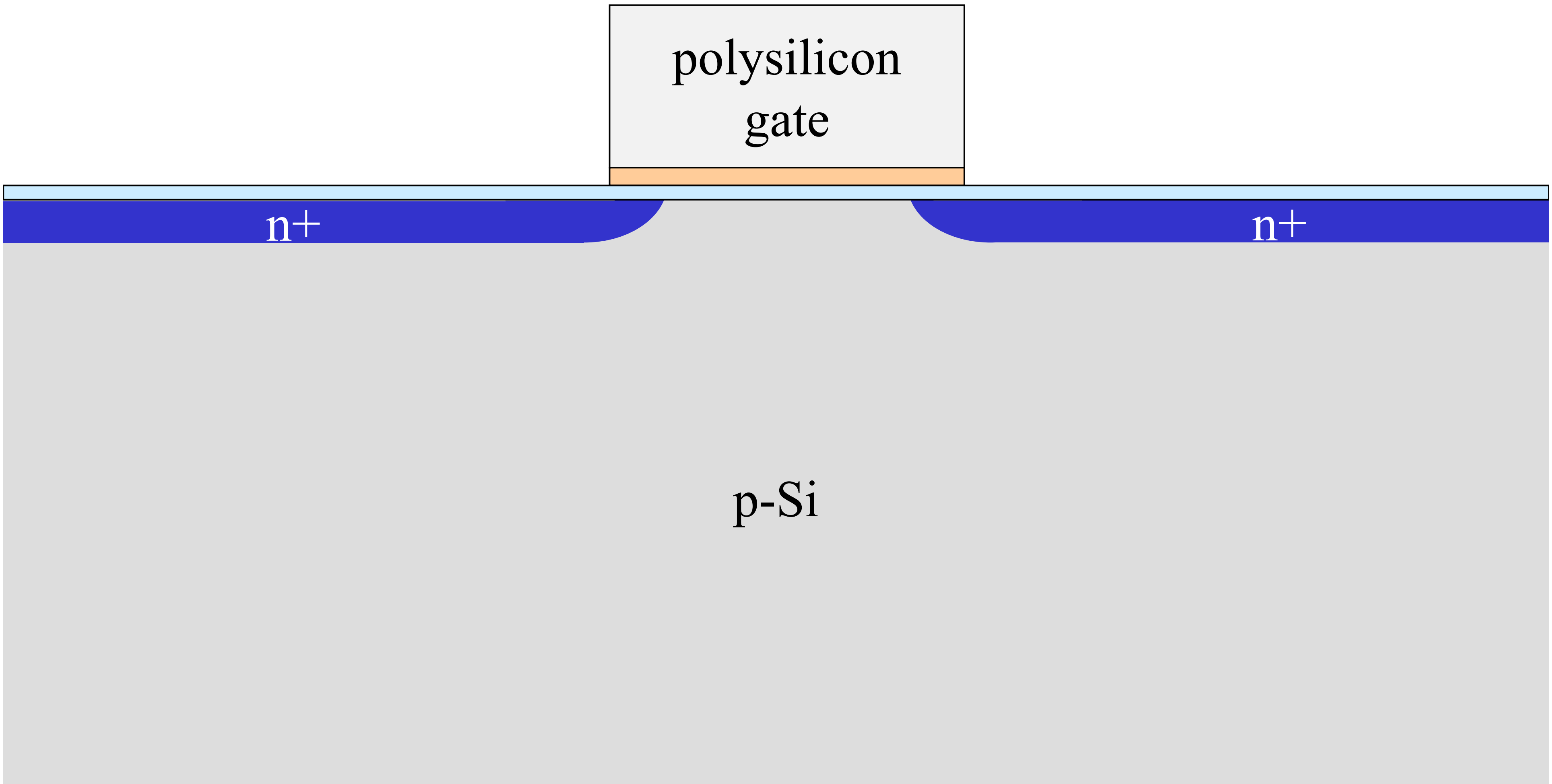

Dry oxidation
SiO_2 gate oxide
p-Si


gate oxide
HfO_2
SiO_2
p-Si

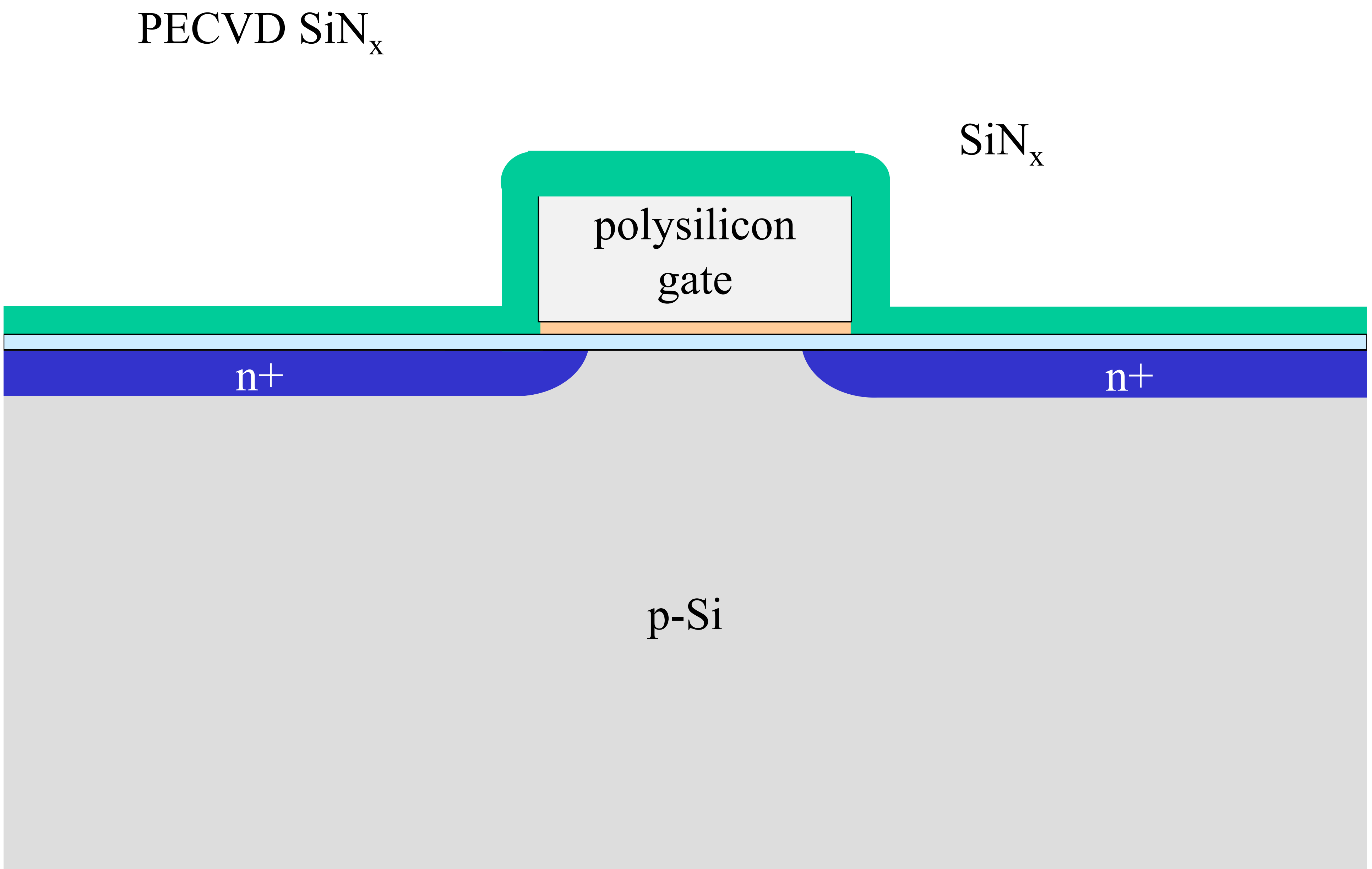

photoresist
polysilicon
CVD: SiH_4 @ 580 to 650 °C
SiO_2/HfO_2
TiN (CVD)
30–70 μΩ·cm Conductive diffusion barrier
p-Si


Implant
polysilicon gate
TiN
SiO_2/HfO_2
Expose resist
Develop
Etch poly and TiN
Strip resist
Implant source and drain
p-Si

Self-aligned fabrication

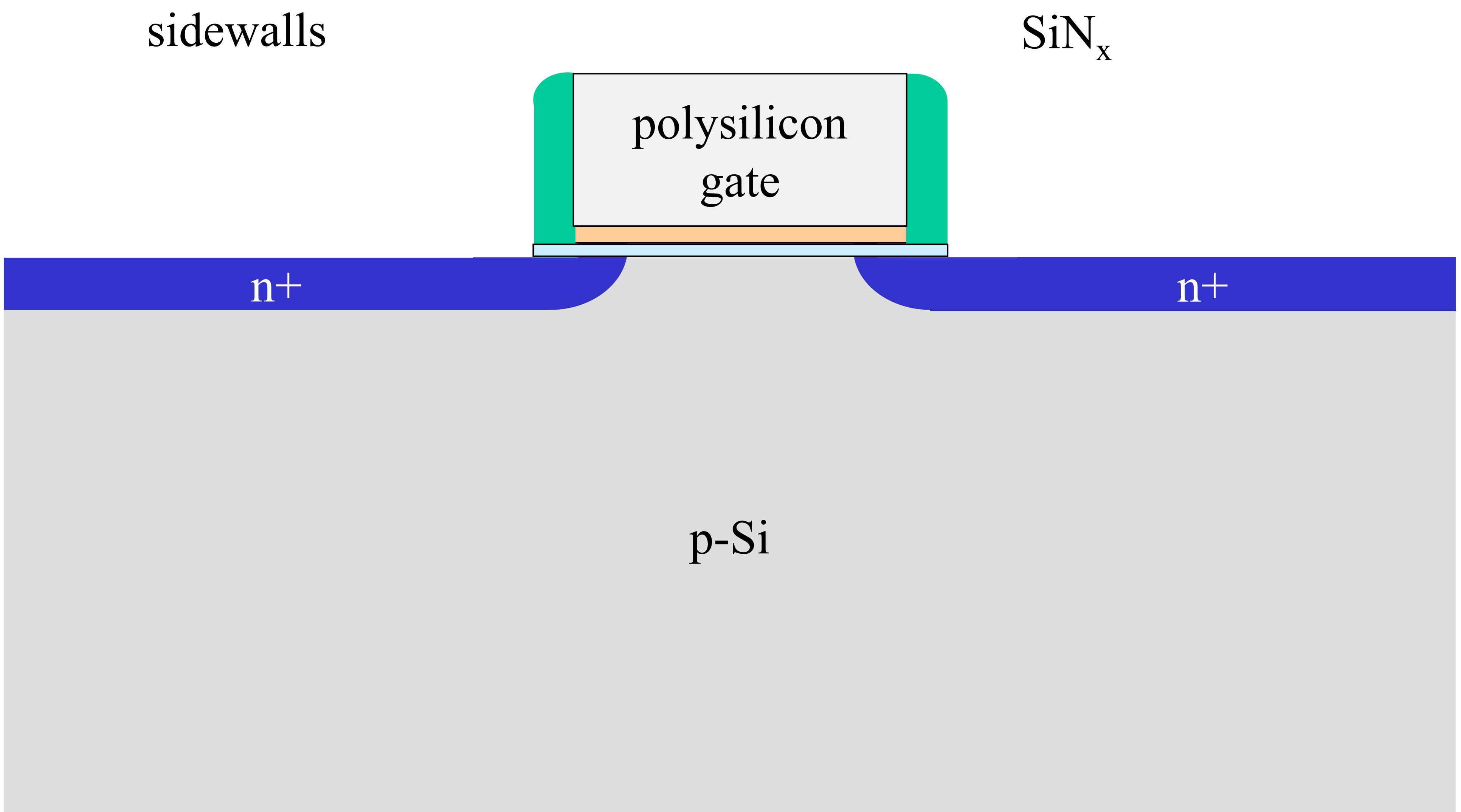


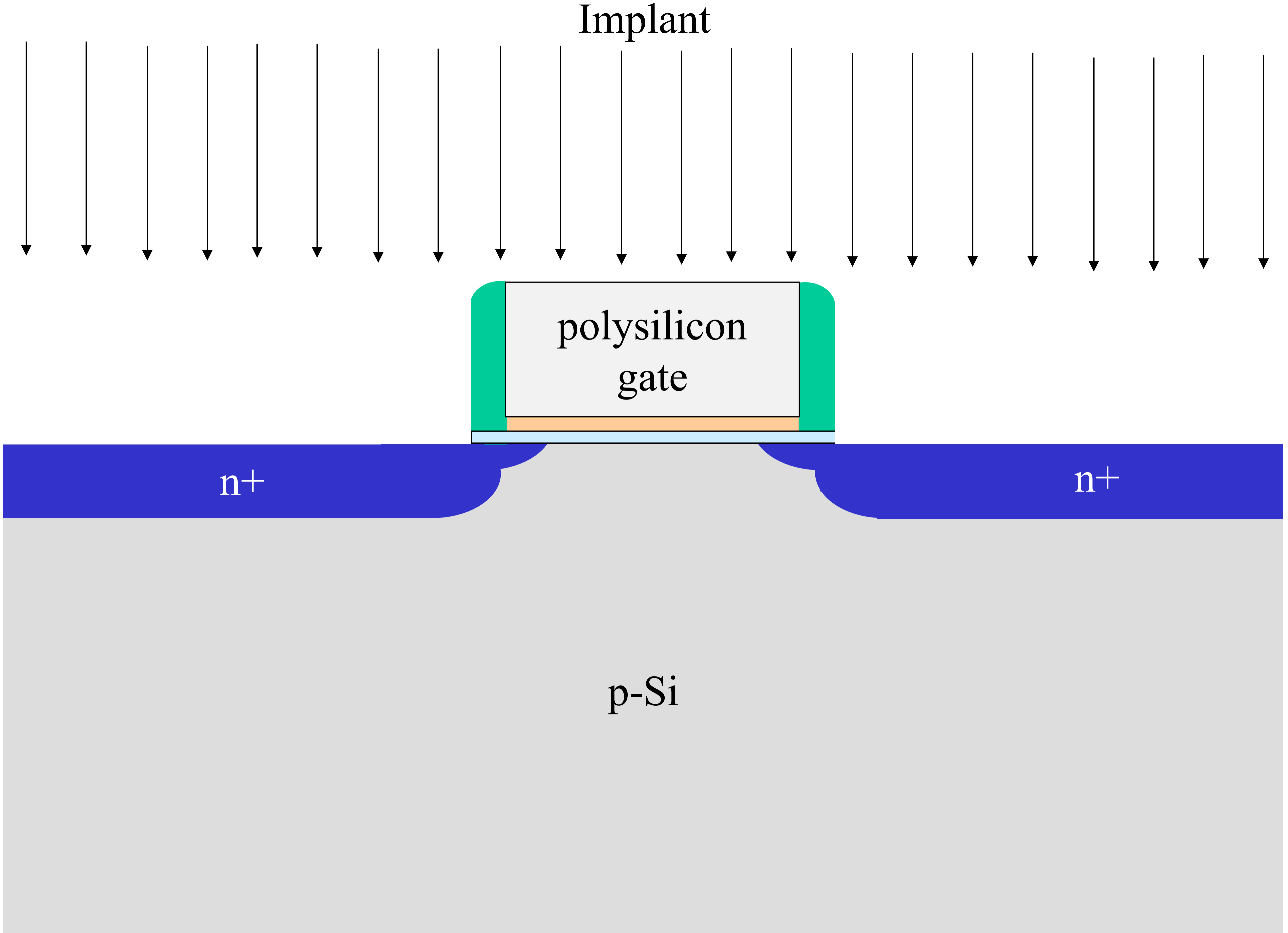
Spacer



Spacer

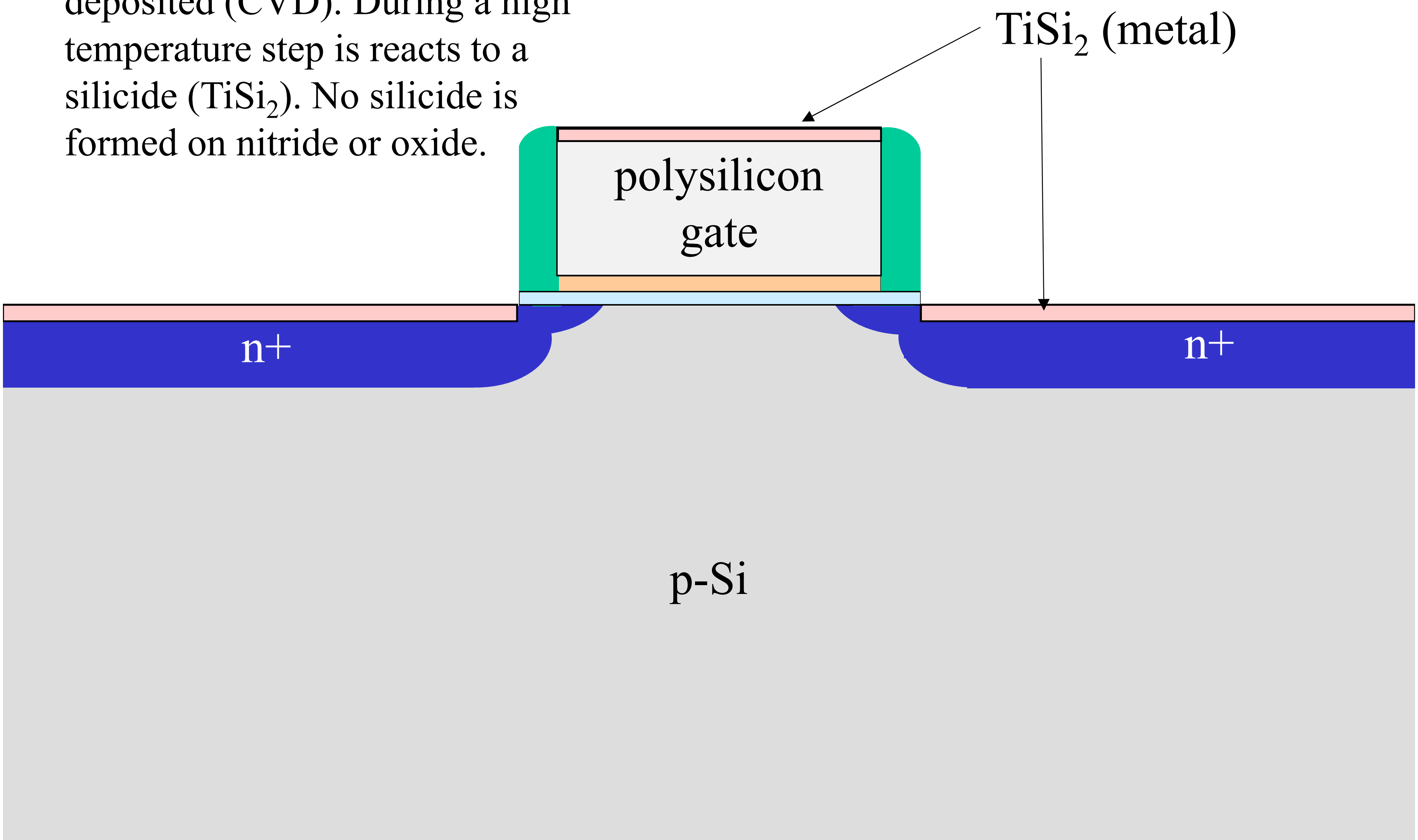
Etch back to leave only sidewalls




Implant
polysilicon
gate
n+
n+
p-Si

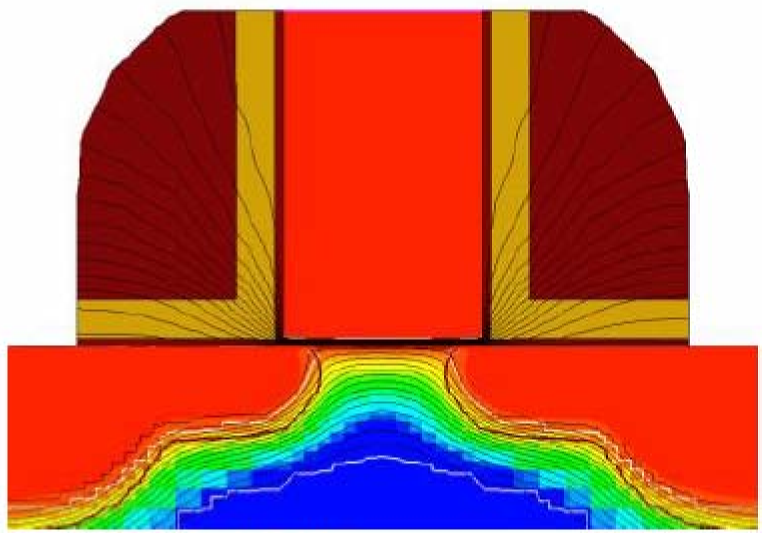
Salicide (Self-aligned silicide)

Transition metal (Ti, Co,W) is deposited (CVD). During a high temperature step is reacts to a silicide ($TiSi_2$). No silicide is formed on nitride or oxide.



Master Thesis:

Modeling and Characterization of Semiconductor Devices at Cryogenic Temperatures



MOSFET in TCAD

CMOS

NMOS is n-channel so it should be in a p-well

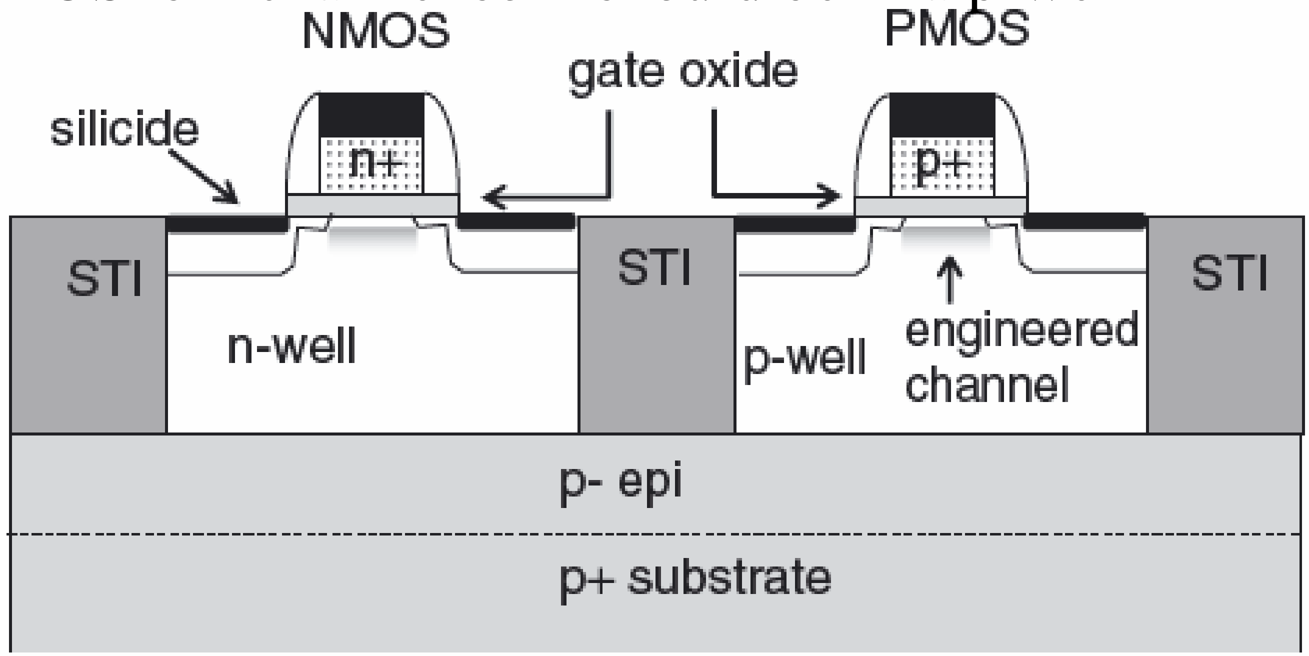
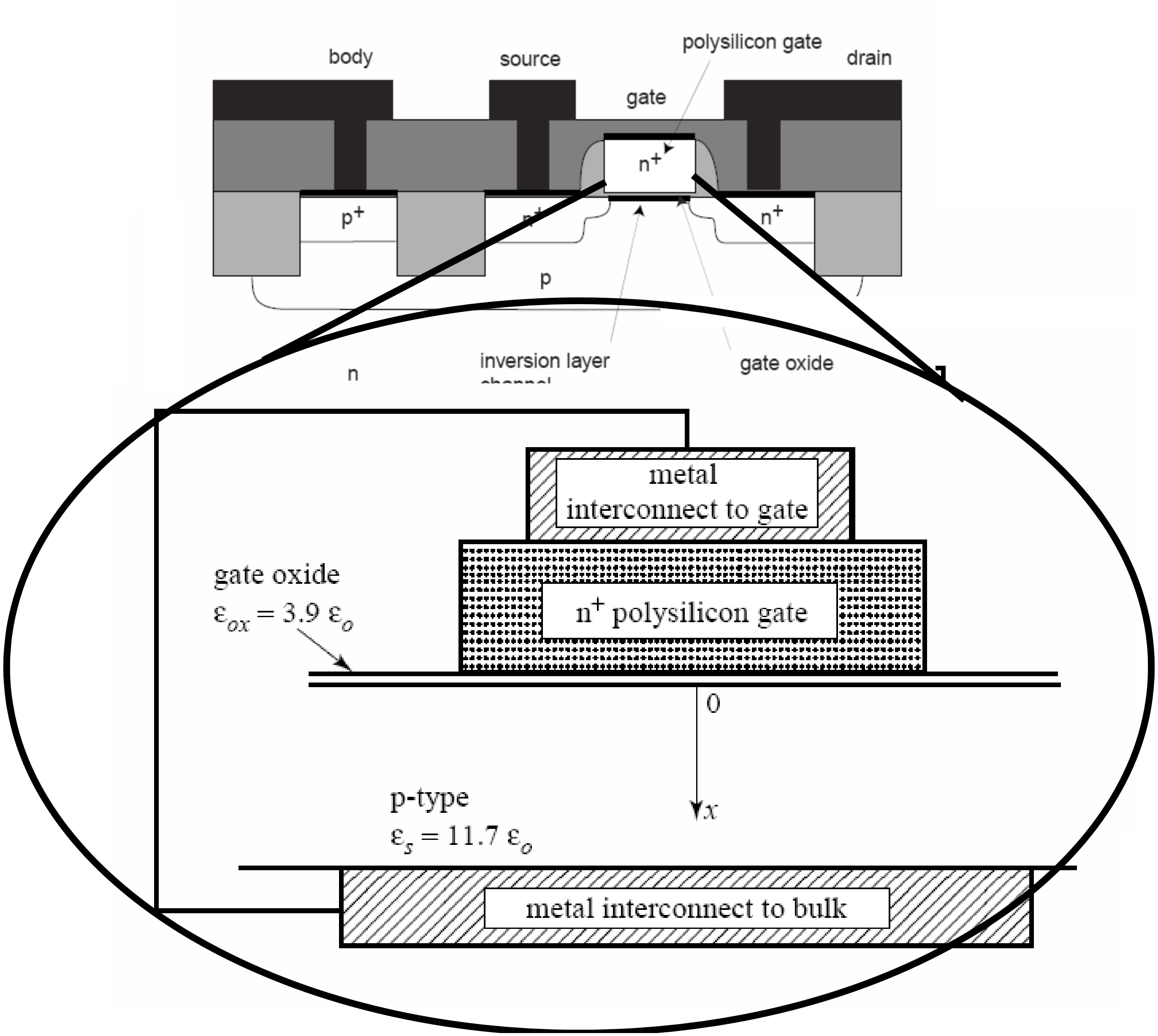


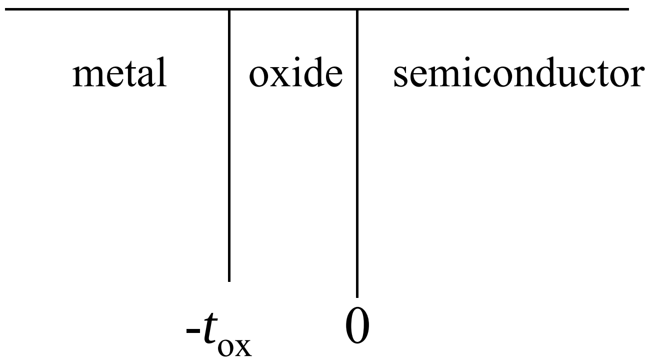
Figure 26.11 Deep submicron CMOS: 200 nm gate length, 5 nm gate oxide, 70 nm junction depth; n^+ poly for NMOS and p^+ poly for PMOS. Shallow trench isolation on epitaxial n^+/p^+ wafer

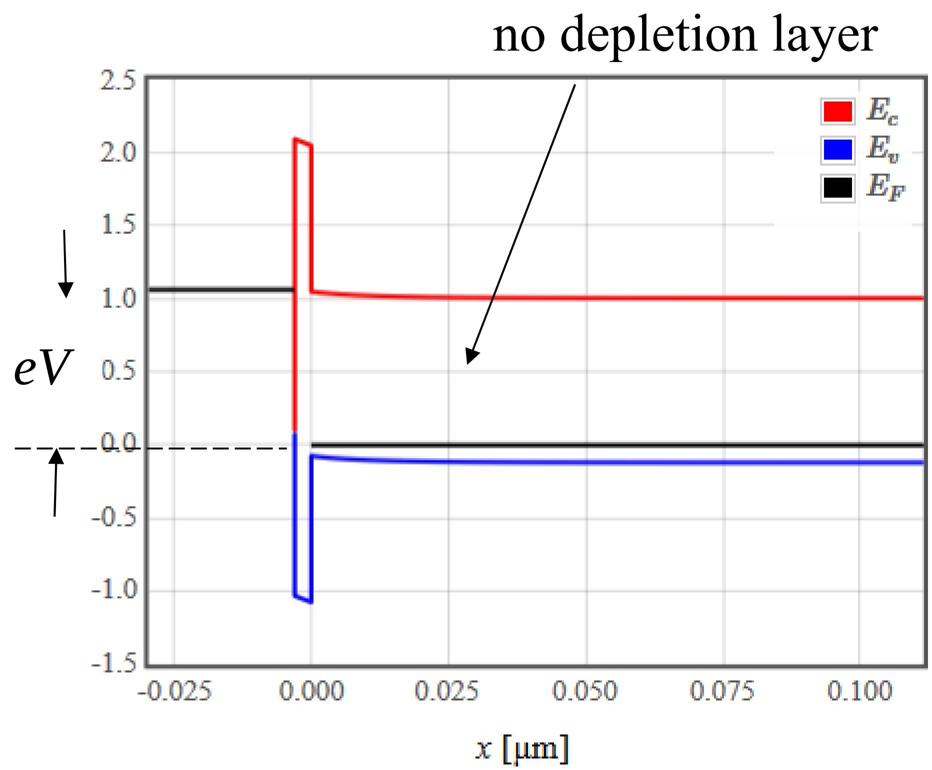
Source: Fransila

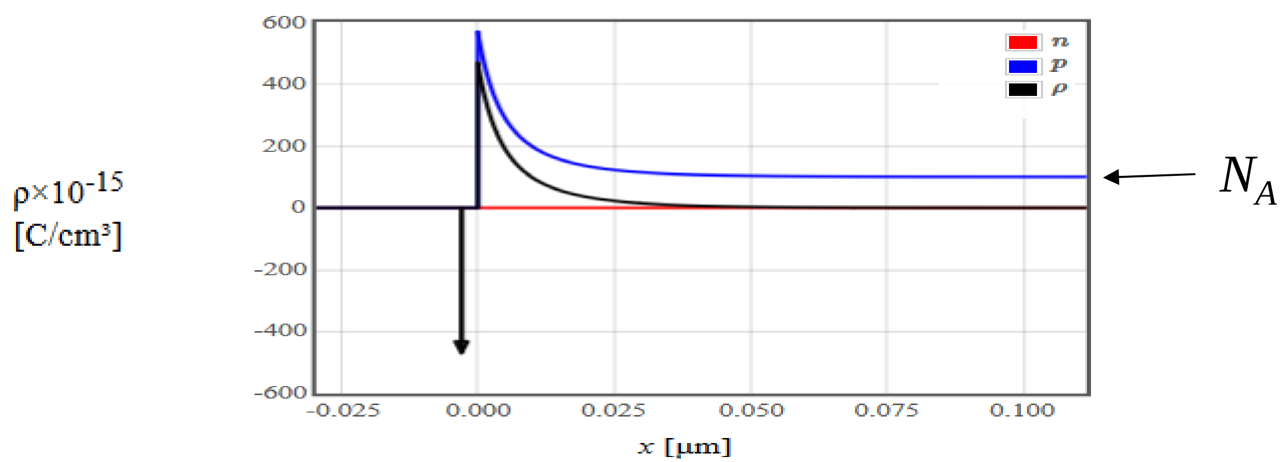
MOS capacitor



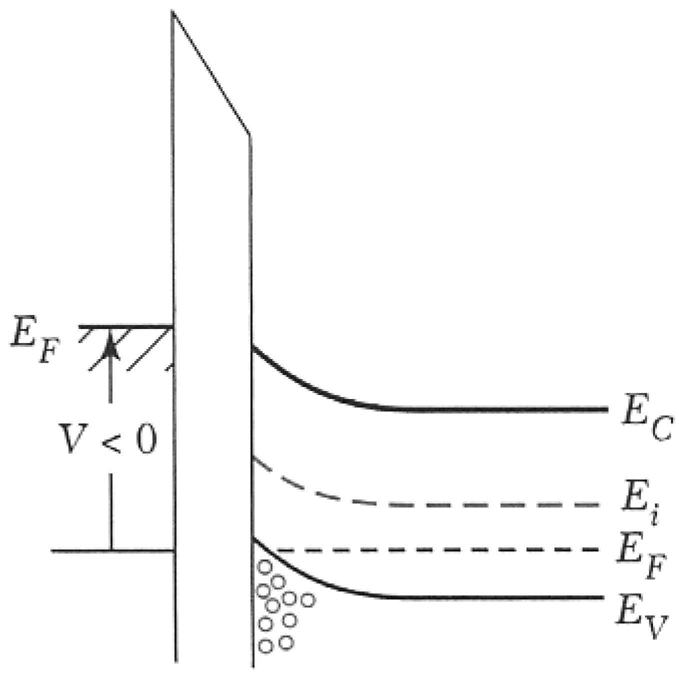
Accumulation

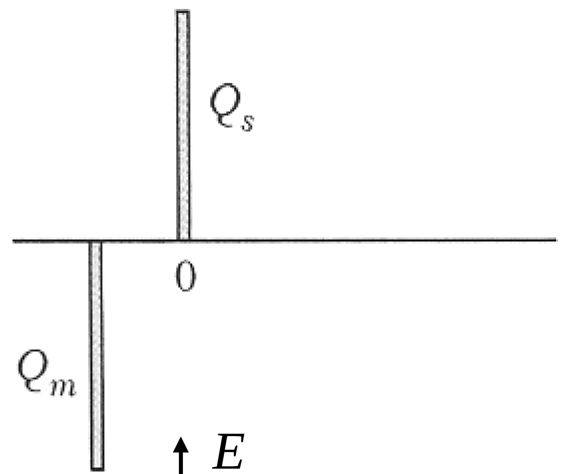


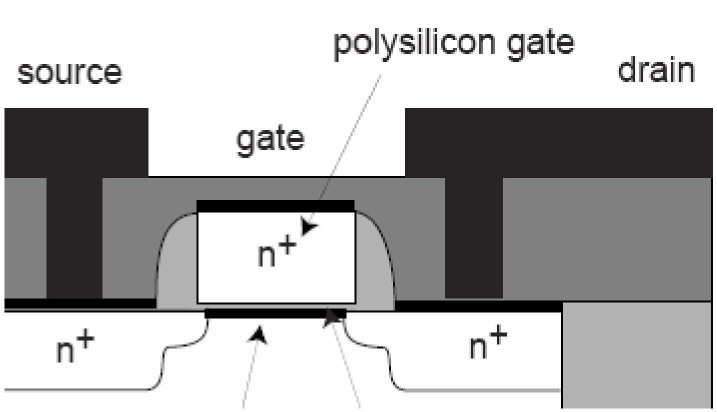


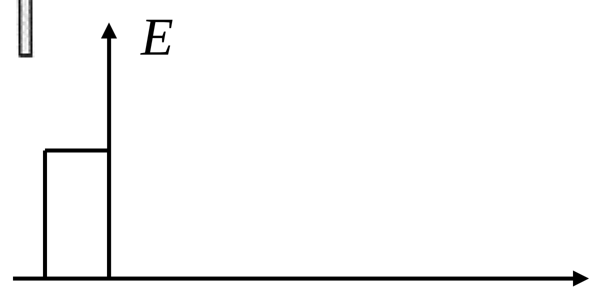


Accumulation

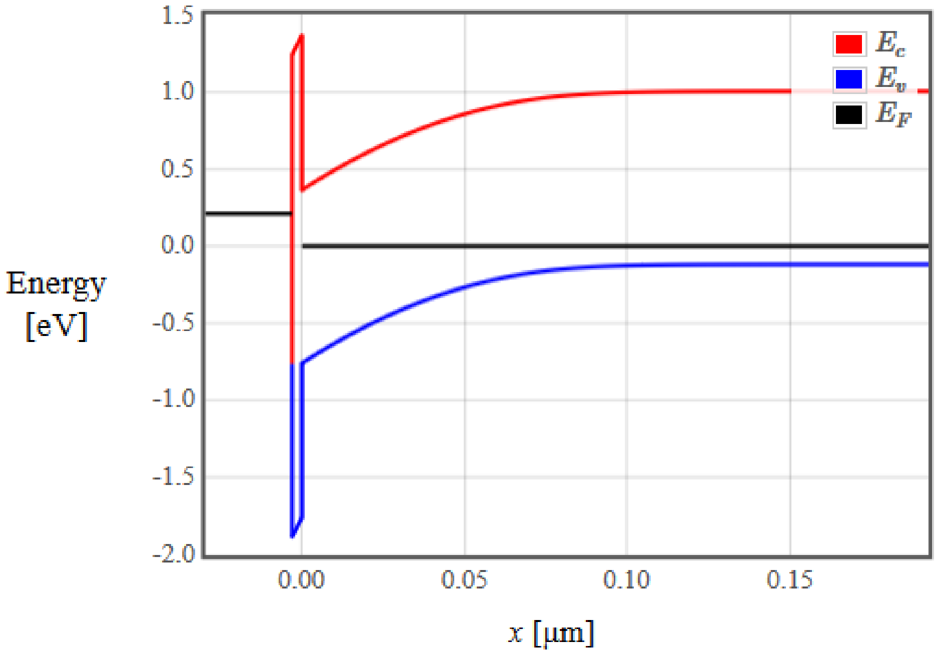


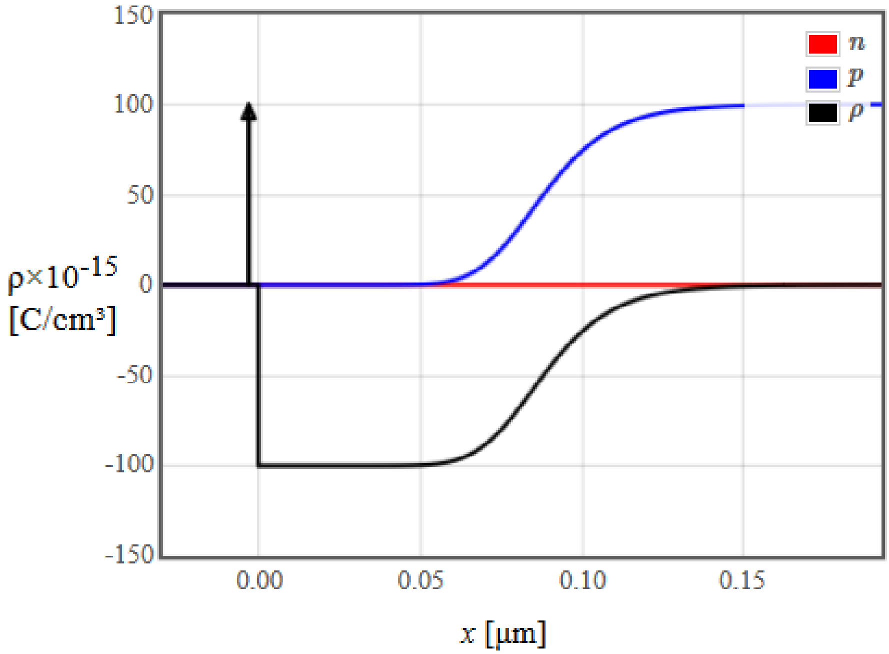




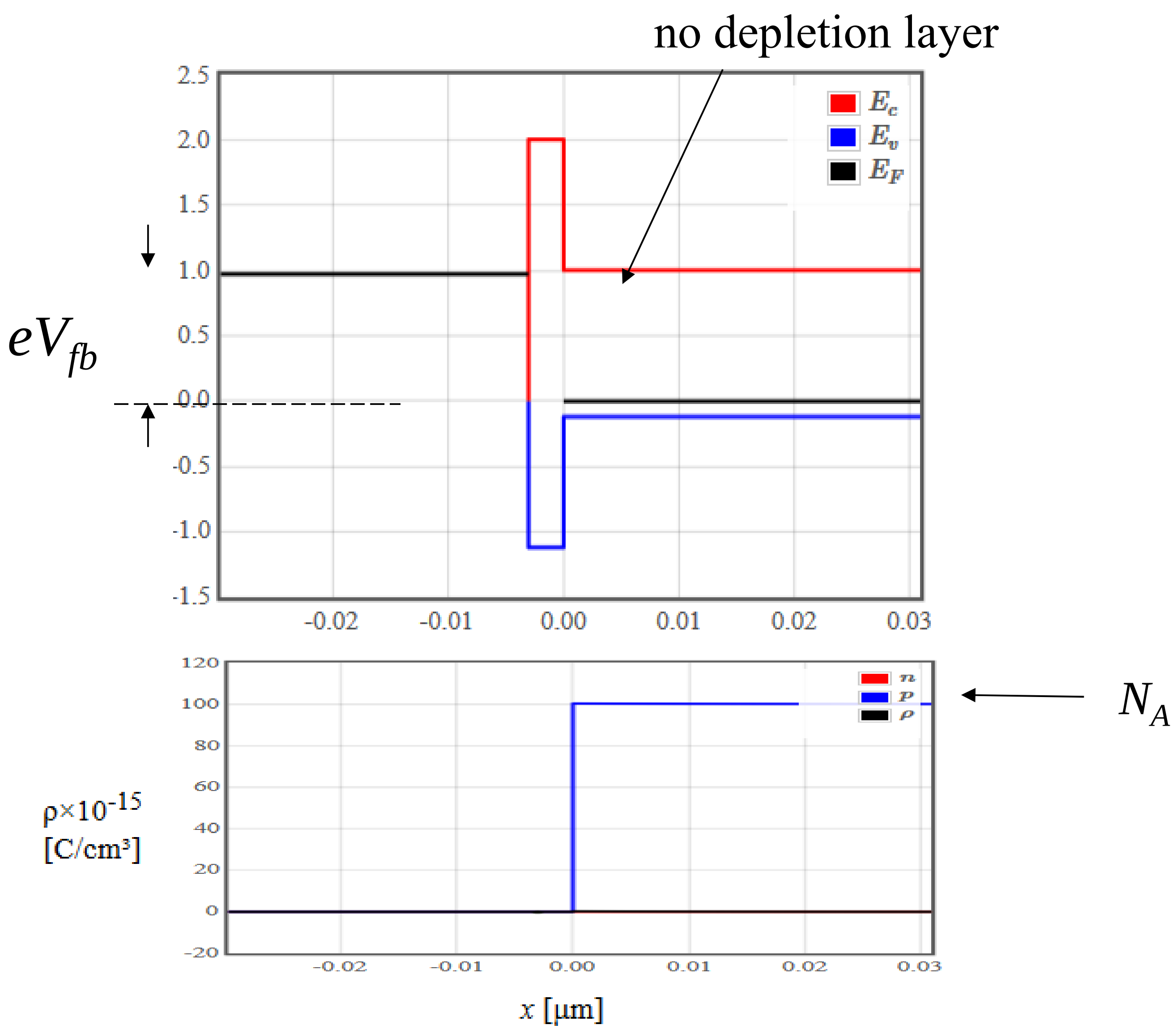


Depletion


Energy
[eV]
1.5
1.0
0.5
0.0
-0.5
-1.0
-1.5
-2.0
0.00
0.05
0.10
0.15
E_c
E_v
E_F
x [μm]

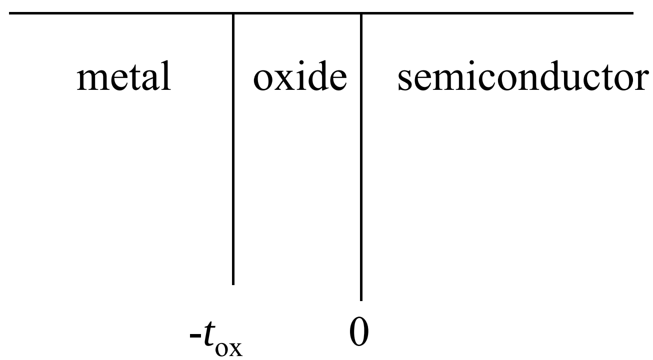

ρ×10^{-15}
[C/cm³]
150
100
50
0
-50
-100
-150
0.00
0.05
0.10
0.15
n
p
ρ
x [μm]

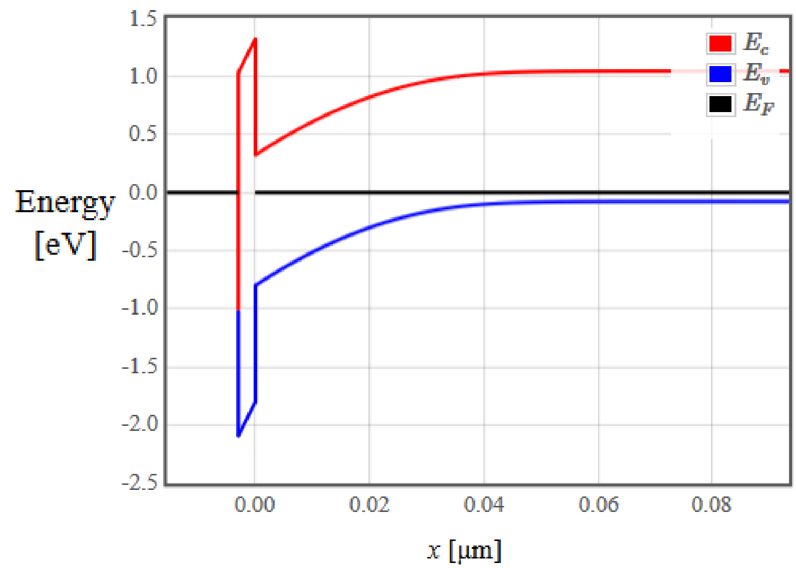
Flat band voltage

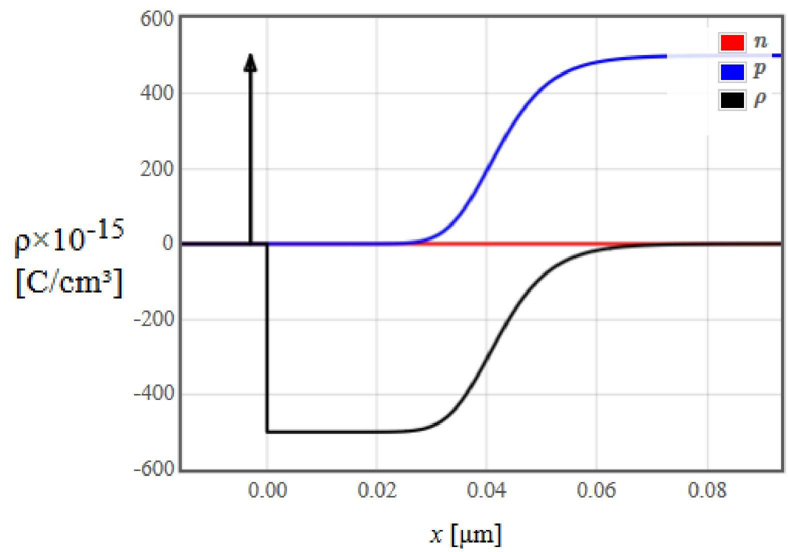


If $\phi_s = \phi_m$, the flatband voltage is the zero bias voltage

Zero bias







$e\phi_m$

Al 4.1 eV

p+ poly 4.05 eV

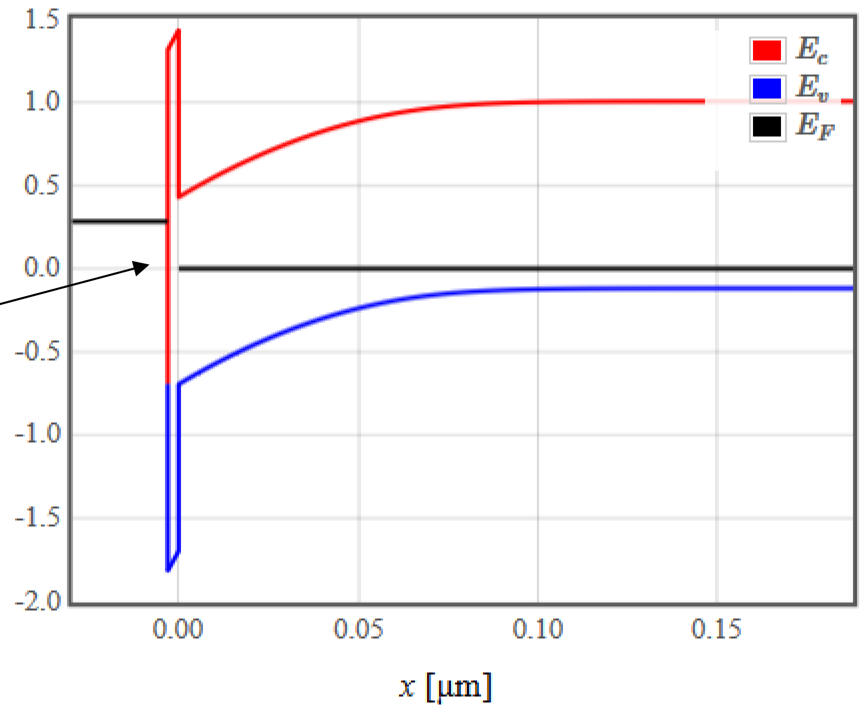
n+ poly 5.05 eV

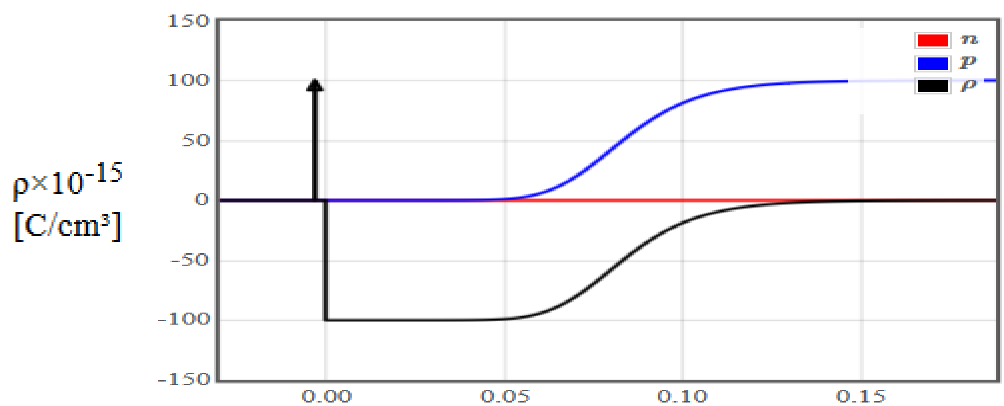
Can be in accumulation or depletion depending on workfunctions

Weak Inversion

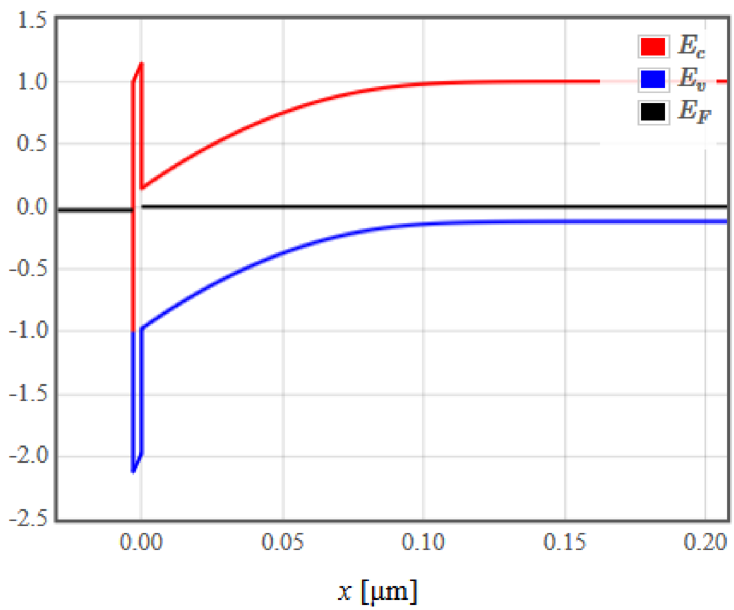
Majority carriers at $x = 0$ change from p to n

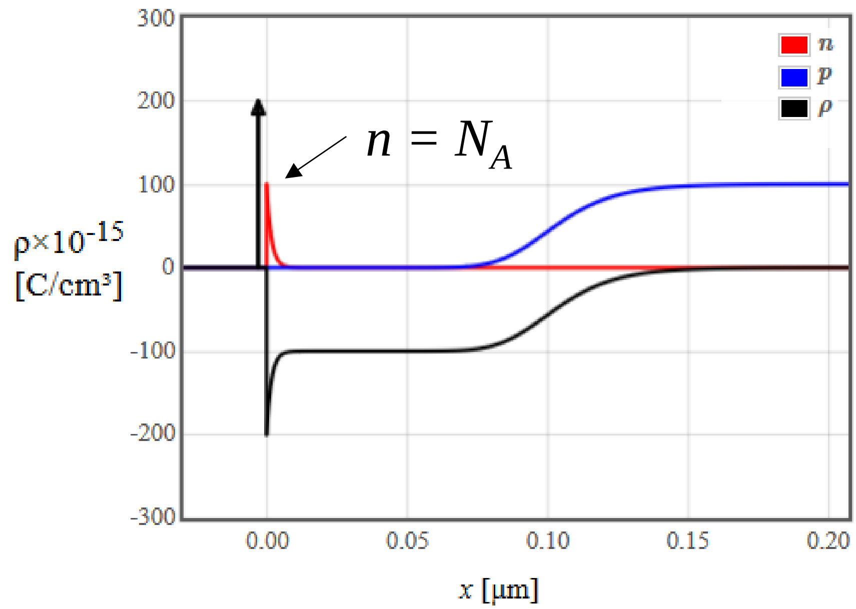
n > p
at the interface





Threshold voltage

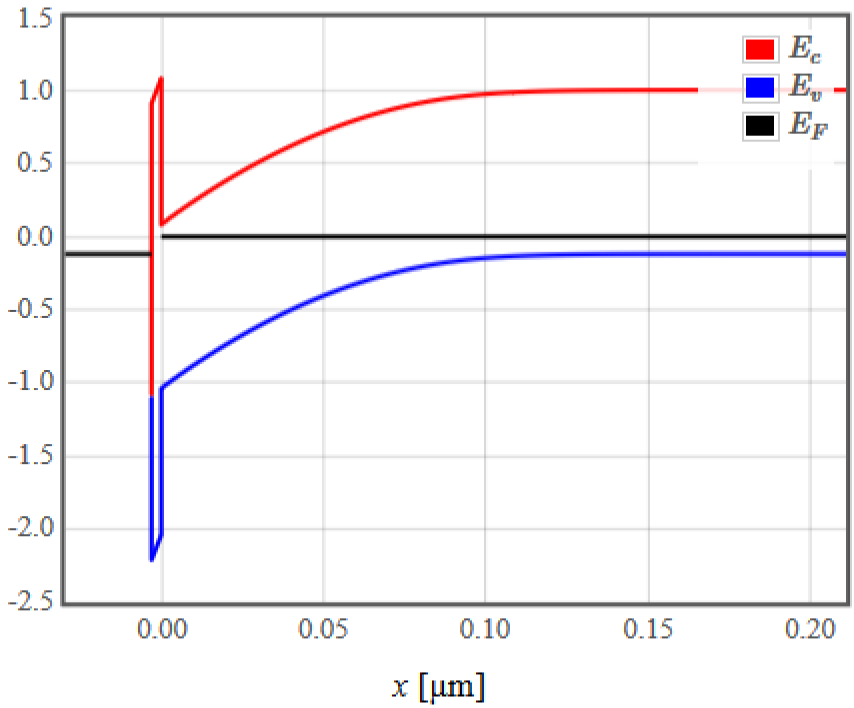


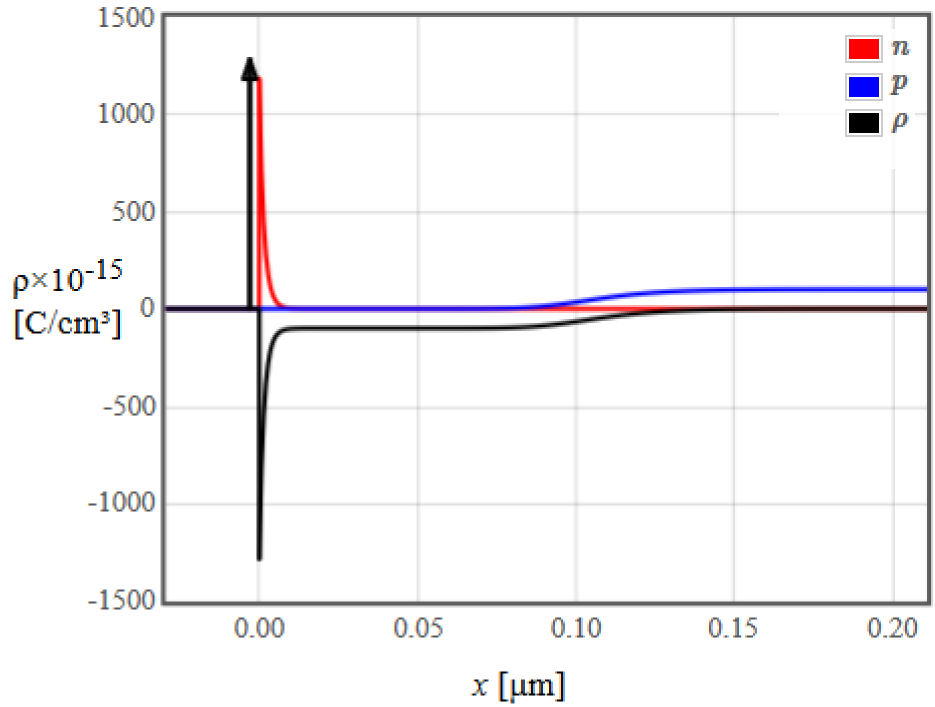


Strong inversion: $n = N_A$ at $x = 0$, the semiconductor-oxide interface

Inversion

$n > N_A$ at $x = 0$, the semiconductor-oxide interface





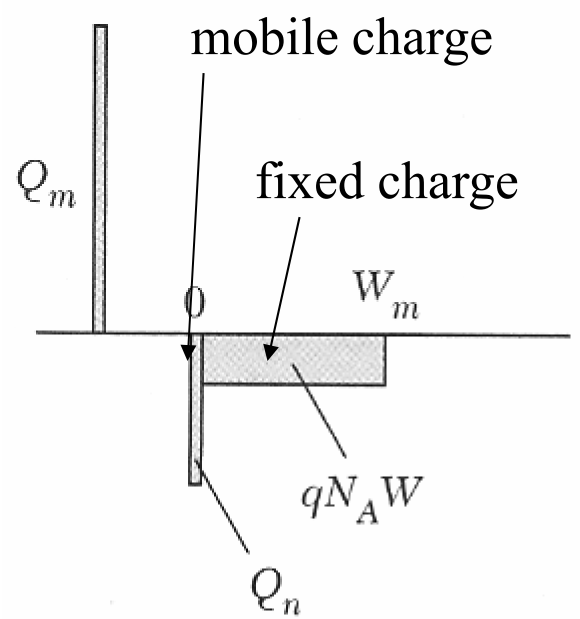
MOS capacitor

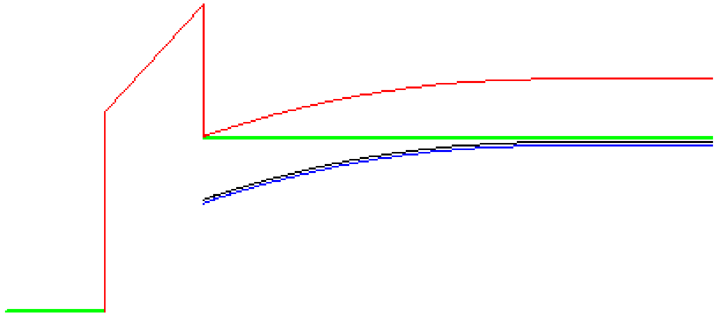
In inversion, the charge in the inversion layer is:

$$Q = -C_{ox}(V_G - V_B - V_T)$$

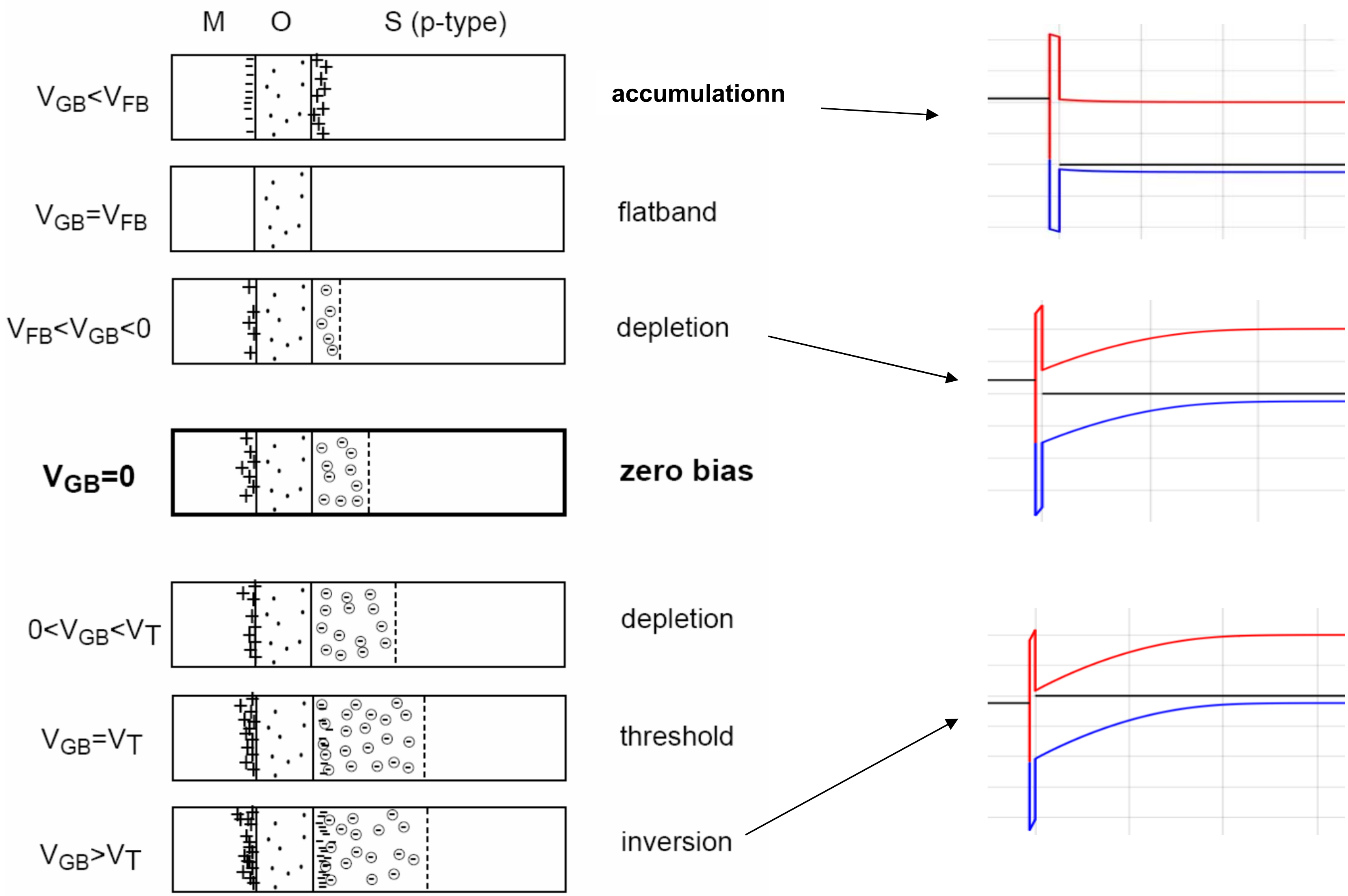
Mobile charge per unit area

Specific capacitance F/m^2

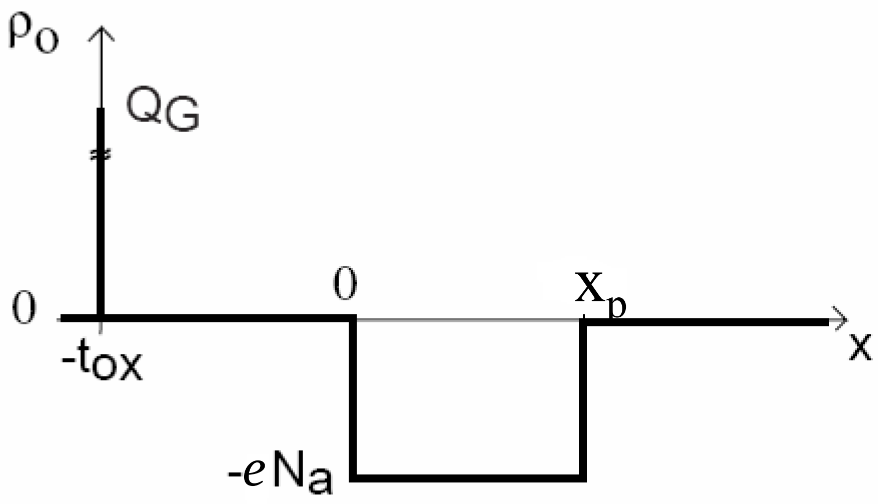




MOS capacitor



charge density (depletion)

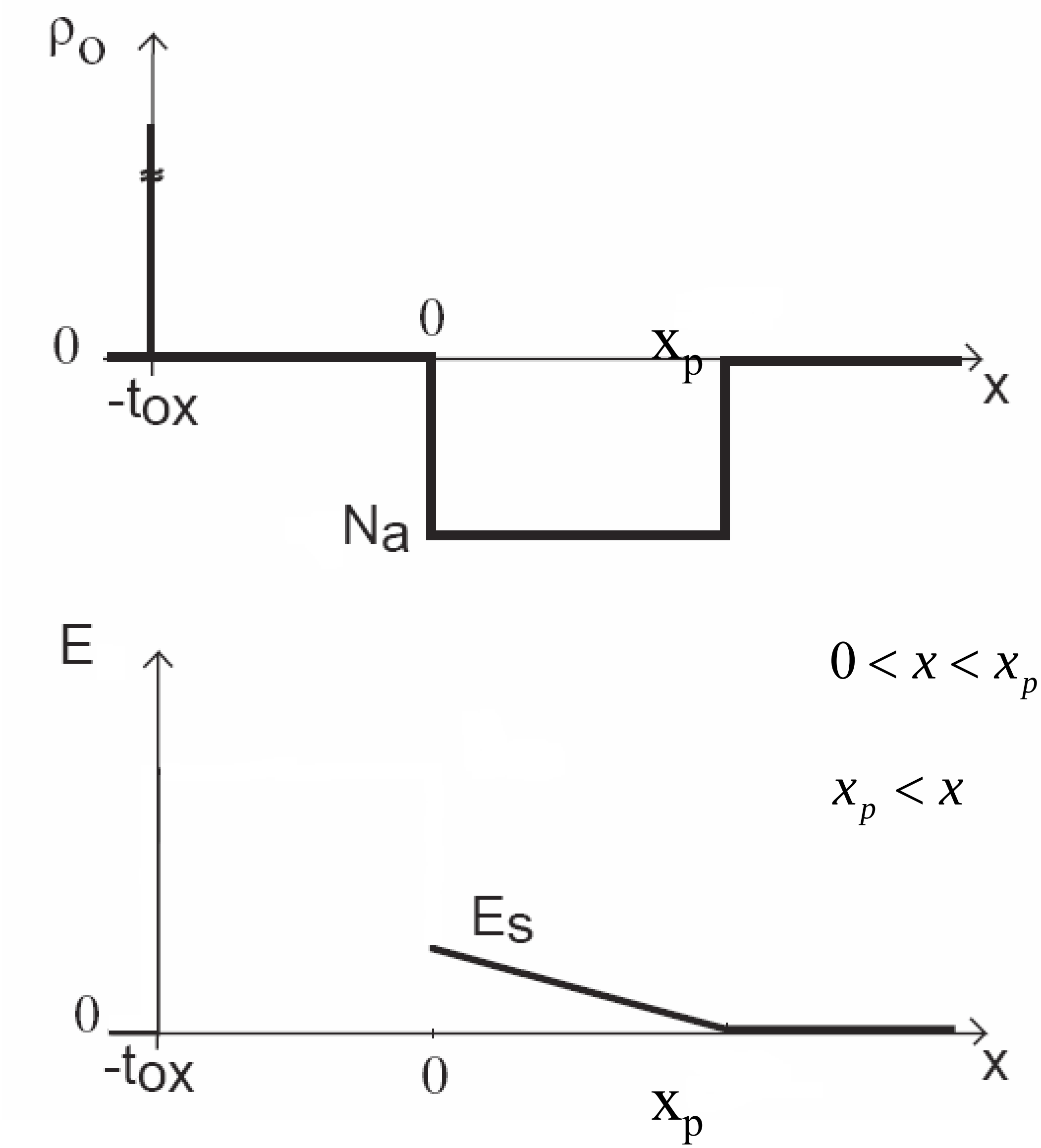


$$-t_{ox} < x < 0 \qquad \rho(x) = 0$$

$$0 < x < x_p \qquad \rho(x) = -eN_A$$

$$x_p < x \qquad \rho(x) = 0$$

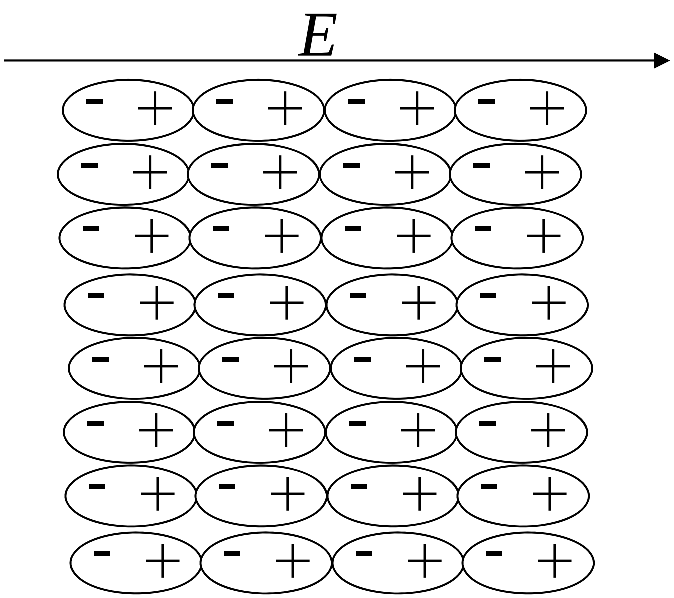
electric field



$0 < x < x_p \qquad E(x) = \frac{-eN_A}{\varepsilon_s}\left(x - x_p\right)$

$x_p < x \qquad E(x) = 0$

electric field (depletion)

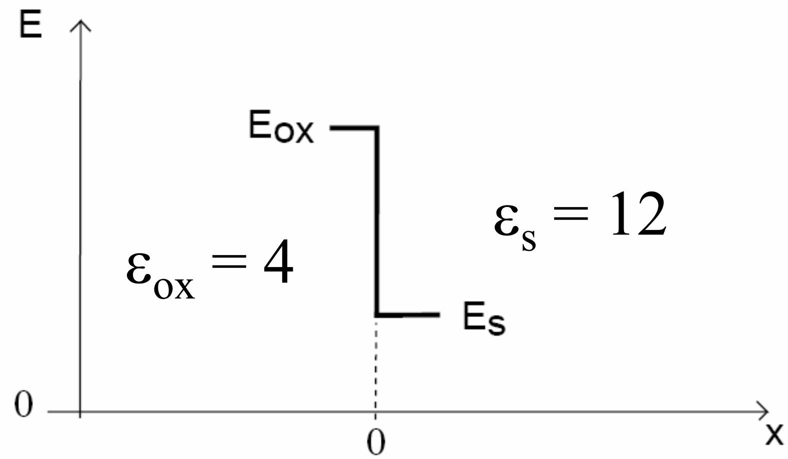


$$\epsilon_{ox} E_{ox} = \epsilon_s E_s$$

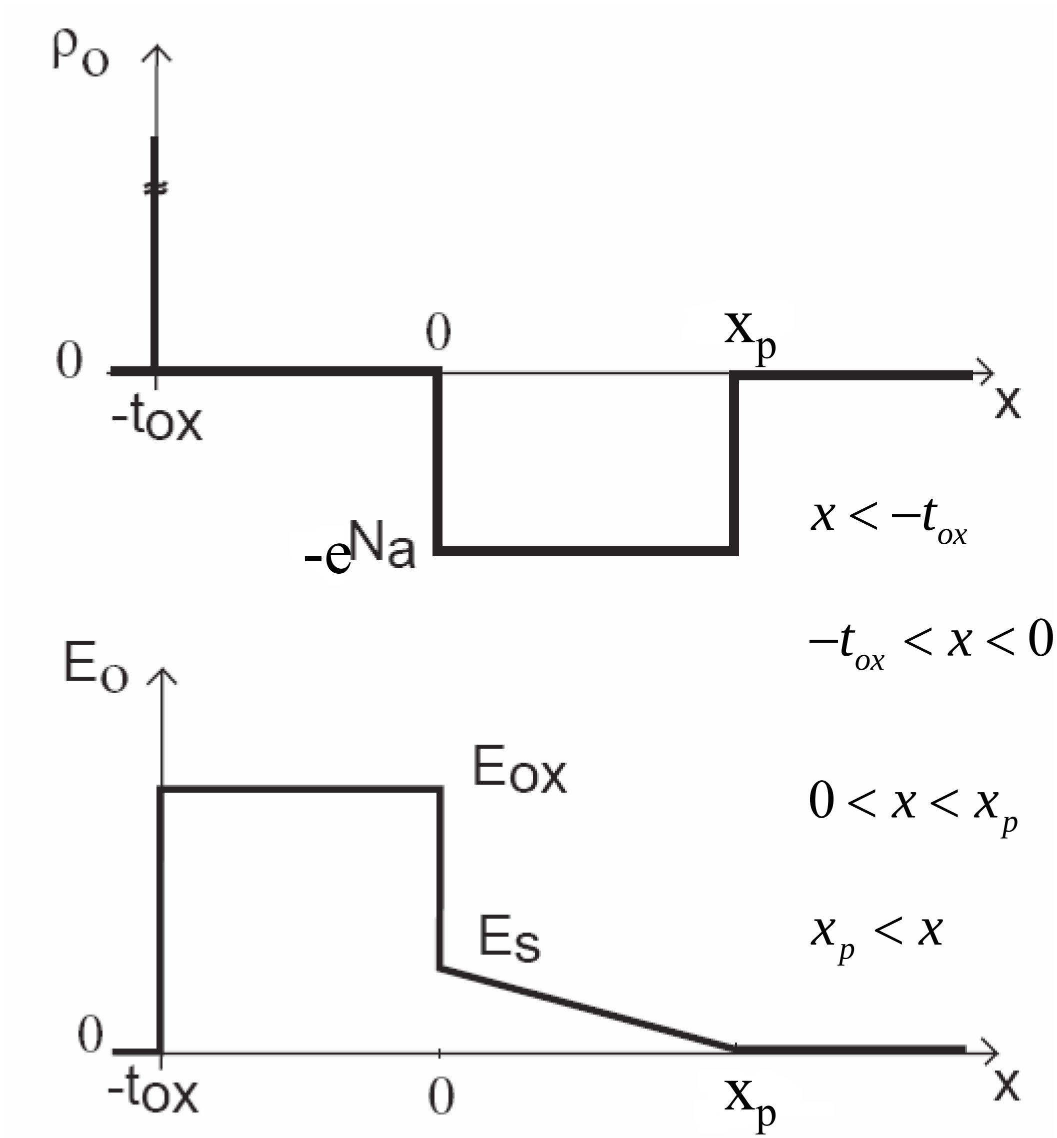
$$\frac{E_{ox}}{E_s} = \frac{\epsilon_s}{\epsilon_{ox}} \simeq 3$$

E is decreased by a factor of the dielectric constant

$$\varepsilon_r = \frac{E_{vacuum}}{E_{dielectric}}$$



electric field



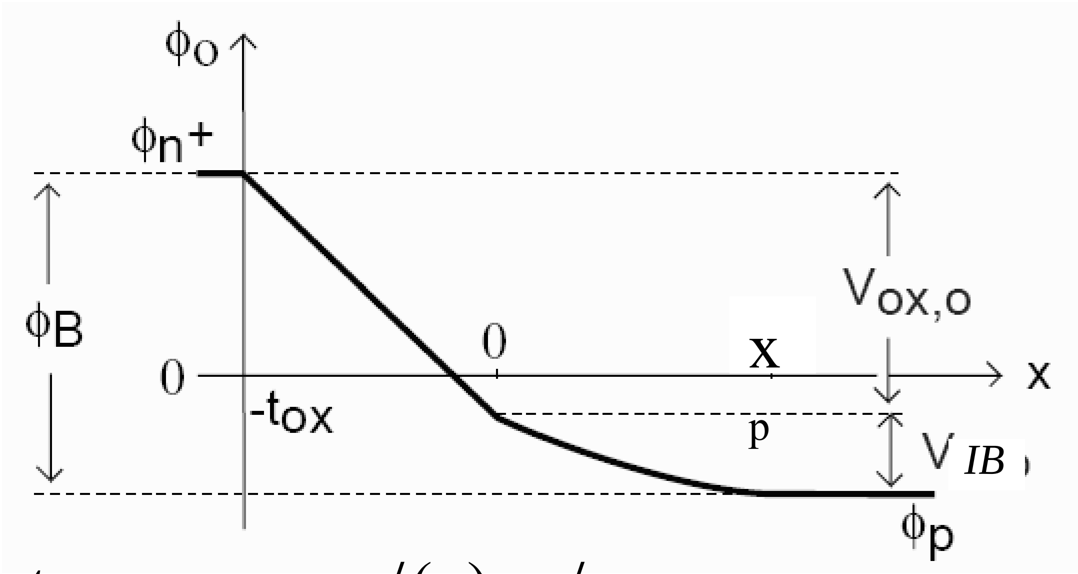
$x < -t_{ox}$ $\quad E(x) = 0$

$-t_{ox} < x < 0$ $\quad E(x) = \dfrac{\varepsilon_S}{\varepsilon_{ox}} E(x = 0^+) = \dfrac{eN_A x_p}{\varepsilon_{ox}}$

$0 < x < x_p$ $\quad E(x) = \dfrac{-eN_A}{\varepsilon_s}\left(x - x_p\right)$

$x_p < x$ $\quad E(x) = 0$

electrostatic potential



$x < -t_{ox}$ $\phi(x) = \phi_{gate}$

$-t_{ox} < x < 0$ $\phi(x) = \phi_p + \frac{eN_A x_p^2}{2\varepsilon_s} + \frac{eN_A x_p}{\varepsilon_{ox}}(-x)$

$0 < x < x_p$ $\phi(x) = \phi_p + \frac{eN_A}{2\varepsilon_s}(x - x_p)^2$

$x_p < x$ $\phi(x) = \phi_p$

(We still don't know x_p)

MOS Capacitor - Solving the Poisson Equation

The app below solves the Poisson equation to determine the band bending, the charge distribution, and the electric field in a MOS capacitor with a p-type substrate.

ϕ_m = 4.08 eV χ_s = 4.05 eV

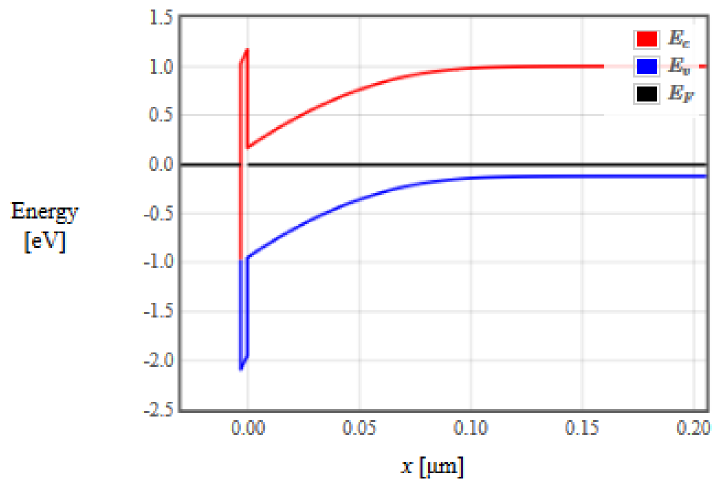
t_{ox} = 3 nm ϵ_{ox} = 4 $N_c(300)$ = 2.78E19 1/cm³ T = 300 K

E_g = 1.166-4.73E-4*T*T/(T+636) eV ϵ_{semi} = 12 $N_v(300)$ = 9.84E18 1/cm³ N_A = 1E17 1/cm³

V = 0 V

- + Submit Si Ge GaAs

Band diagram



$E_g = 1.12$ eV $n_i = 6.40e+9$ 1/cm³

$E_s = 1.57e+7$ V/m $V_s = 0.831$ V

$Q = -0.00167$ C/m²

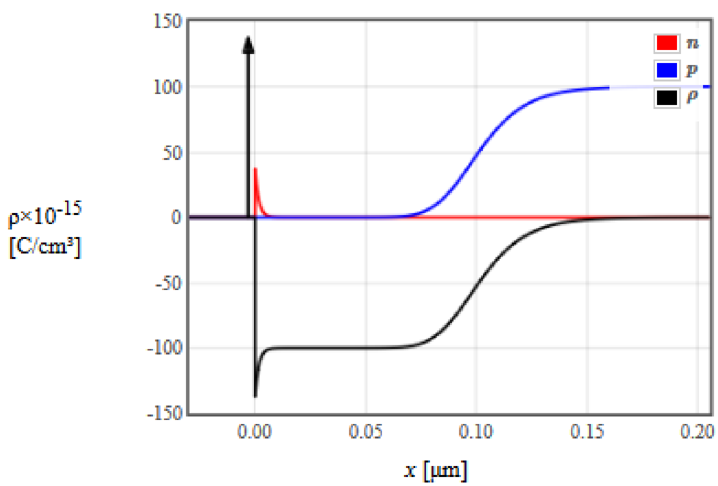
$E_{ox} = 4.70e+7$ V/m $V_{shoot} = 0.0000221$ V

$\phi_s = 5.05$ eV $V_{fb} = \phi_m - \phi_s = -0.972$ V

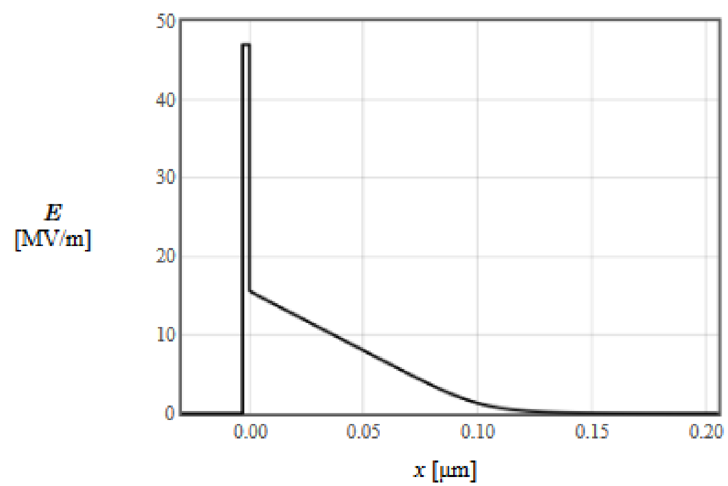
From the depletion approximation:

$\max(x_p)$ 0.107 µm $V_T = 0.0292$ V

Charge density



Electric field



Band bending at inversion

$n = N_A$ at threshold

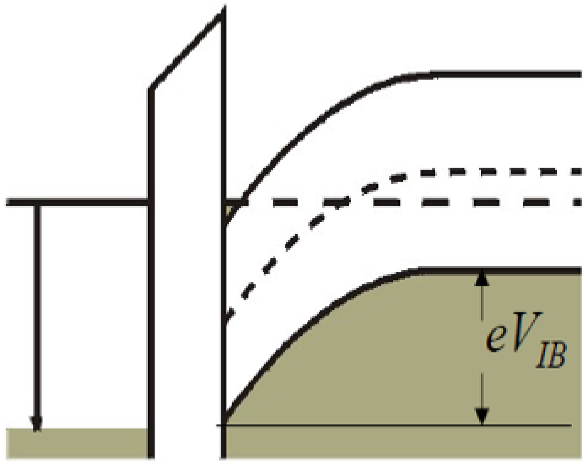
Far on the p side

$$n = \frac{n_i^2}{N_A} = N_c \exp\left(\frac{E_F - E_c}{k_B T}\right) \qquad E_F - E_c = k_B T \ln\left(\frac{n_i^2}{N_A N_c}\right)$$

At the interface, $n = N_A$

$$N_A = N_c \exp\left(\frac{E_F - E_c}{k_B T}\right) \qquad E_F - E_c = k_B T \ln\left(\frac{N_A}{N_c}\right)$$

The voltage between the semiconductor-oxide interface and the body



V_{IB} is the voltage between the interface and the body

$$eV_{IB} = k_B T \ln\left(\frac{N_A}{N_c}\right) - k_B T \ln\left(\frac{n_i^2}{N_A N_c}\right)$$

Strong inversion

$n_s = N_A$ at the semiconductor-oxide interface

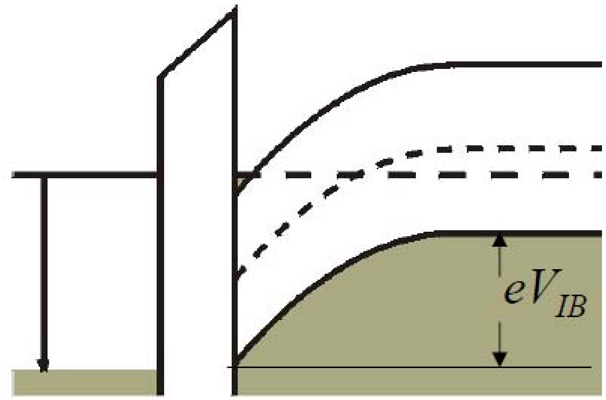
$$eV_{IB} = k_B T \ln\left(\frac{N_A}{N_c}\right) - k_B T \ln\left(\frac{n_i^2}{N_A N_c}\right)$$

$$\ln(a) - \ln(b) = \ln\left(\frac{a}{b}\right)$$

$$eV_{IB} = k_B T \ln\left(\frac{N_A^2}{n_i^2}\right)$$

$$\ln\left(a^2\right) = 2\ln(a)$$

$$eV_{IB} = 2k_B T \ln\left(\frac{N_A}{n_i}\right)$$



The depletion width remains constant in inversion.

Depletion width in inversion

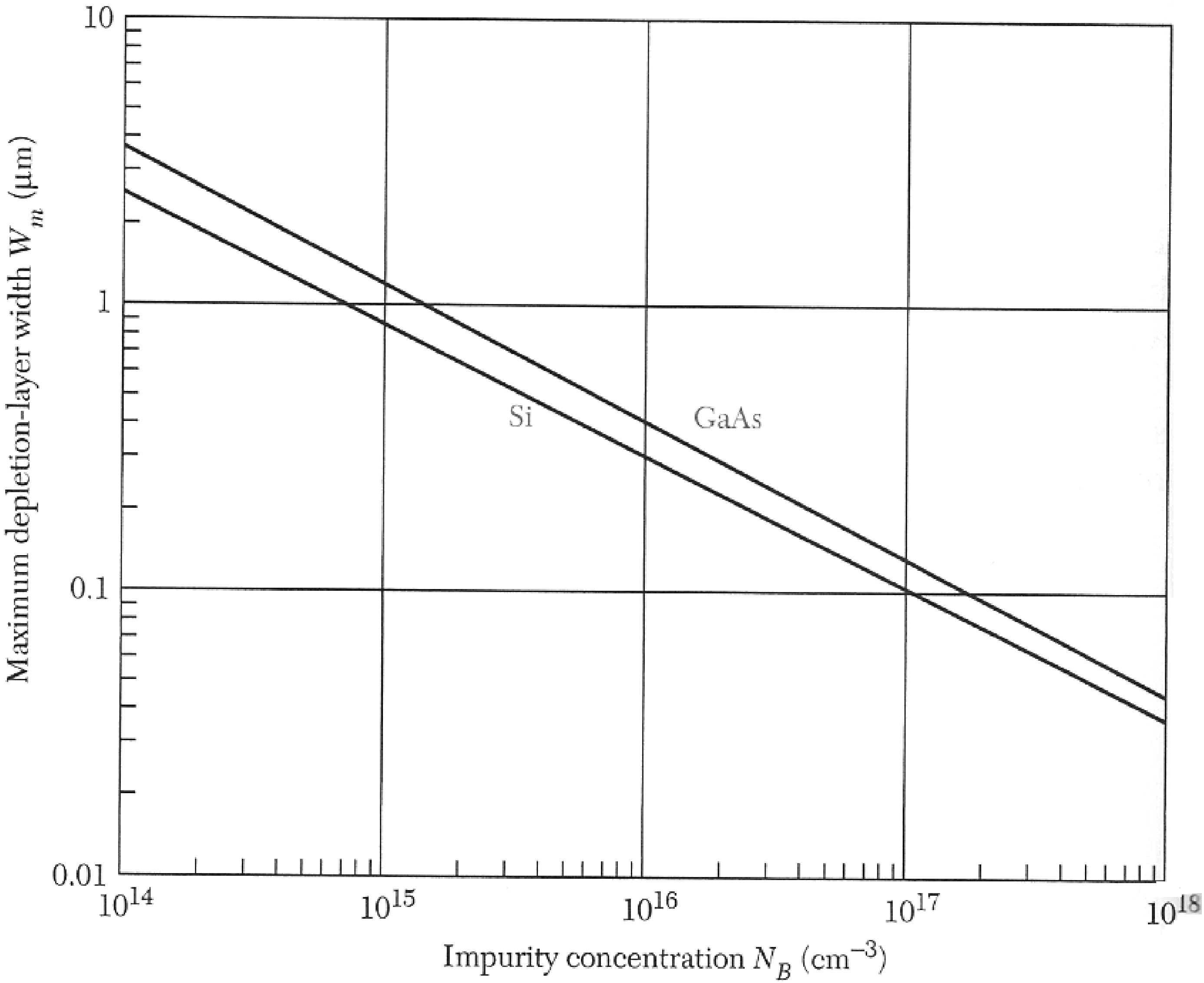
$$V_{IB} = \frac{eN_A x_p^2}{2\varepsilon}$$

$$eV_{IB} = 2k_B T \ln\left(\frac{N_A}{n_i}\right)$$

$$x_{p(\max)} = \sqrt{\frac{2\varepsilon V_{IB}}{eN_A}} = 2\sqrt{\frac{\varepsilon}{e^2 N_A} k_B T \ln\left(\frac{N_A}{n_i}\right)}$$

The depletion width remains constant in inversion.

Depletion width



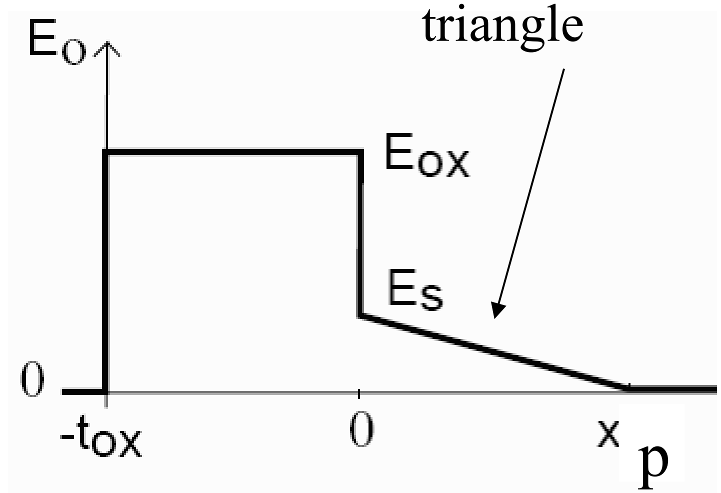
Electric field at semi-oxide interface at strong inversion

$$eV_{IB}(\text{strong inversion}) = 2k_BT\ln\left(\frac{N_A}{n_i}\right)$$

$$E_s = 2\frac{V_{IB}}{x_{p(\max)}} = \frac{2V_{IB}}{\sqrt{\frac{2\varepsilon V_{IB}}{eN_A}}} = 2\sqrt{\frac{N_A}{\varepsilon}k_BT\ln\left(\frac{N_A}{n_i}\right)}$$

$$E_{ox} = \frac{\varepsilon}{\varepsilon_{ox}}E_s = \frac{2\varepsilon}{\varepsilon_{ox}}2\sqrt{\frac{N_A}{\varepsilon}k_BT\ln\left(\frac{N_A}{n_i}\right)}$$

$V_{IB} = E_s x_p/2 =$ area of the triangle



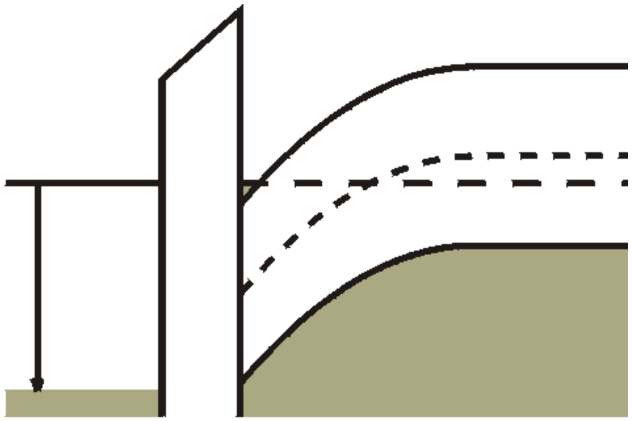
Threshold voltage

$$V_T = E_{ox}\left(\text{strong inversion}\right)t_{ox} + V_{IB}\left(\text{strong inversion}\right) + V_{FB}$$

$$V_T = \frac{2\varepsilon t_{ox}}{\varepsilon_{ox}}\sqrt{\frac{N_A k_B T \ln\left(\frac{N_A}{n_i}\right)}{\varepsilon}} + 2\frac{k_B T}{e}\ln\left(\frac{N_A}{n_i}\right) + V_{FB}$$

$$\frac{\varepsilon t_{ox}}{\varepsilon_{ox}} E_{inversion}$$

$$V_{IB}$$

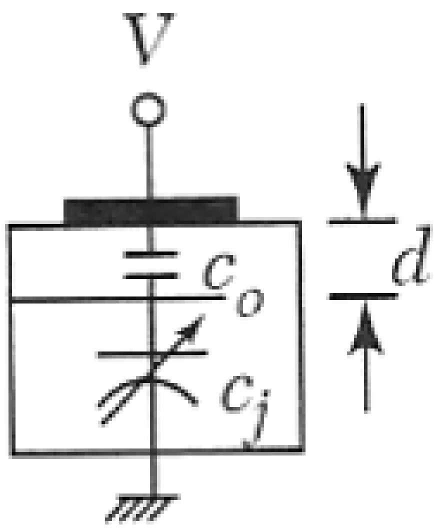


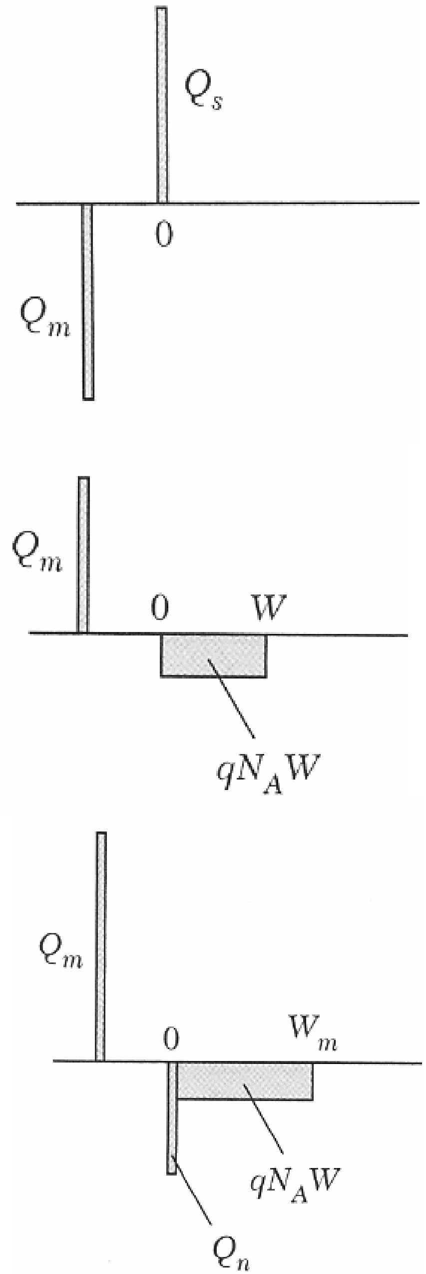
Small V_T requires a small t_{ox} and a large ε_{ox}.

MOS capacitance

$$C_{ox} = \frac{\varepsilon_{ox}}{t_{ox}} \qquad C_j = \frac{\varepsilon}{x_p}$$

$$C = \left(\frac{1}{C_{ox}} + \frac{1}{C_j} \right)^{-1}$$





MOS Capacitor - Capacitance voltage

In capacitance-voltage profiling, the capacitance of a MOS capacitor is measured as a function of the bias voltage. The app below solves the Poisson equation to determine the charge-voltage and capacitance voltage characteristics of a MOS capacitor with a p-type substrate. This is the low-frequency result. At high frequencies, the charge at the oxide interface does not change fast enough and the characteristics take on another form.

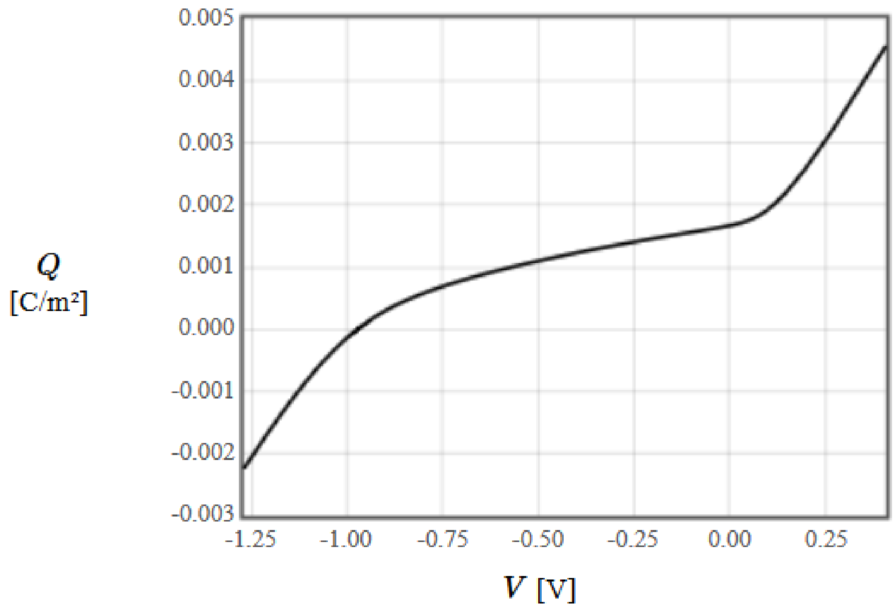
$\phi_m =$ 4.08 eV $\chi_s =$ 4.05 eV

$t_{ox} =$ 3 nm $\epsilon_{ox} =$ 4 $N_c(300) =$ 2.78E19 1/cm³ $T =$ 300 K

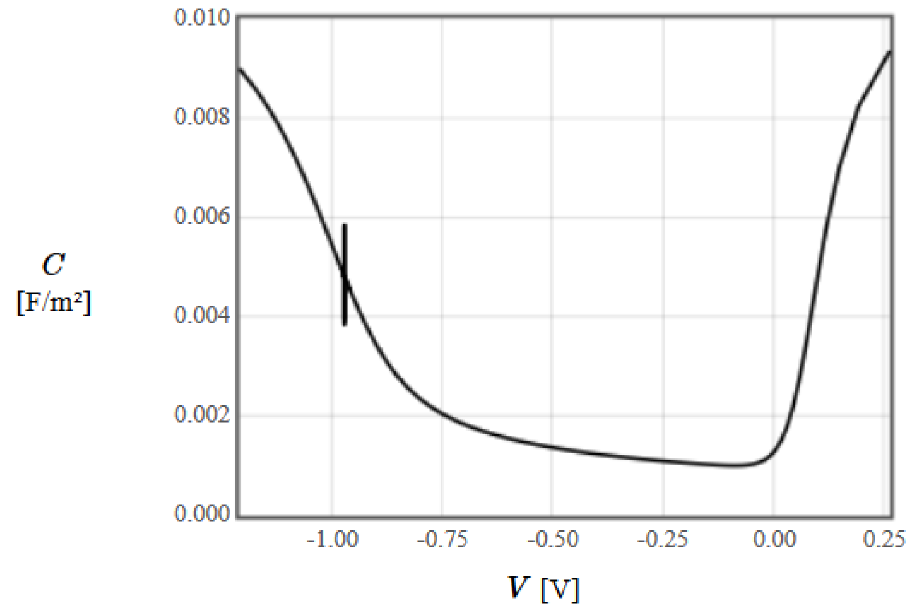
$E_g =$ 1.166-4.73E-4*T*T/(T+636) eV $\epsilon_{semi} =$ 12 $N_v(300) =$ 9.84E18 1/cm³ $N_A =$ 1E17 1/cm³

Submit   Si   Ge   GaAs

Q - V



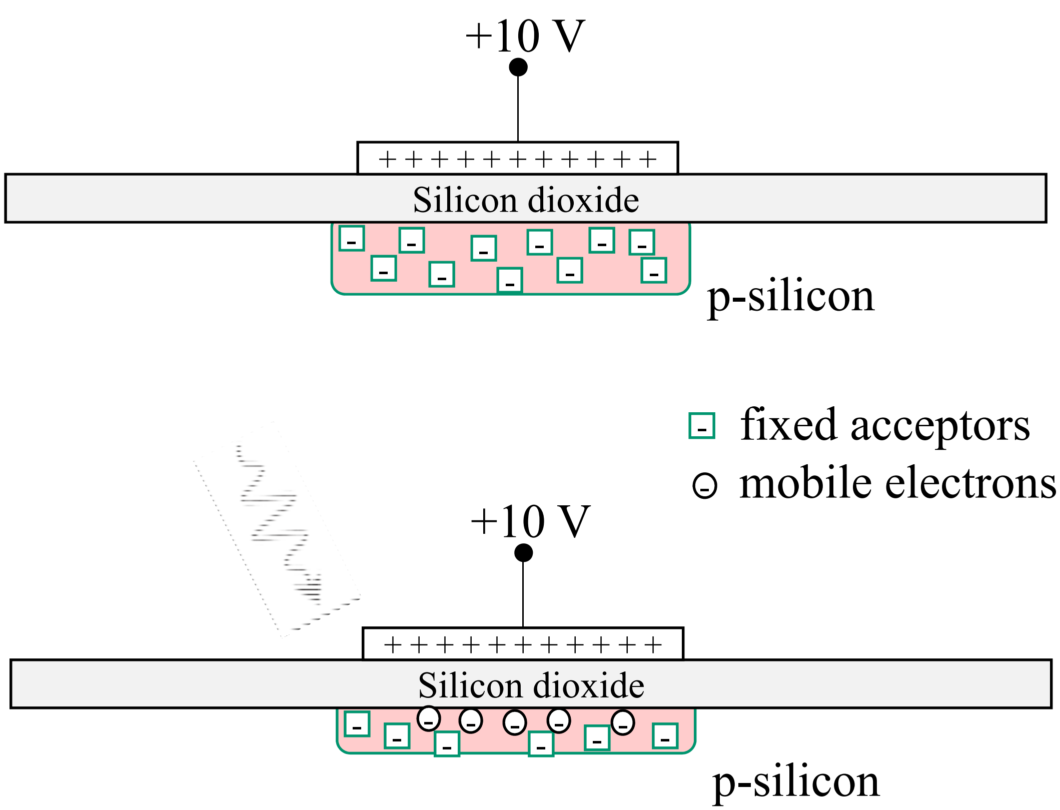
C - V

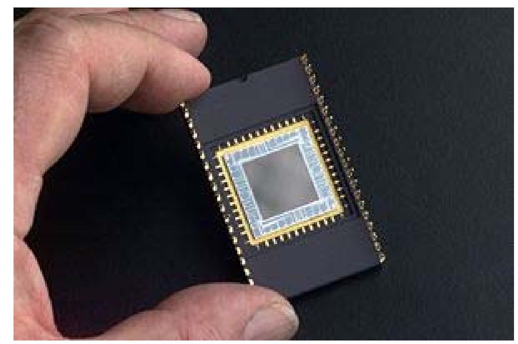


$E_g = 1.12$ eV $n_i = 6.40\text{e+}9$ 1/cm³ $\phi_s = 5.05$ eV $V_{fb} = \phi_m - \phi_s = -0.972$ V

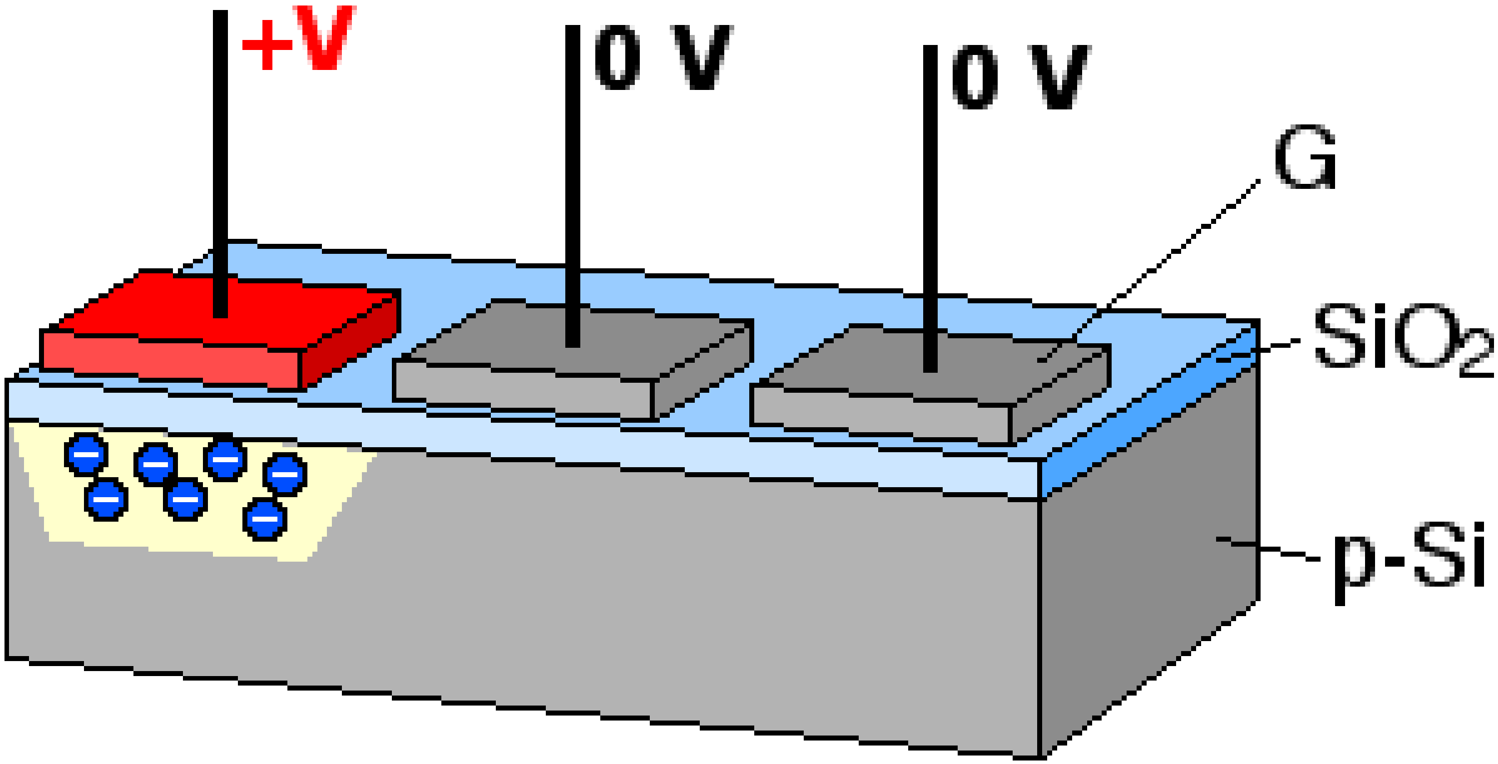
$C_{ox} = \frac{\epsilon_{ox}}{t_{ox}} = 0.0118$ F/m² $V_T = 0.0292$ V

CCD devices


+10 V
+ + + + + + + + + + + +
Silicon dioxide
p-silicon
fixed acceptors
mobile electrons
+10 V
+ + + + + + + + + + + +
Silicon dioxide
p-silicon



CCD devices



https://en.wikipedia.org/wiki/Charge-coupled_device#/media/File:CCD_charge_transfer_animation.gif